

Electronic Materials and Devices

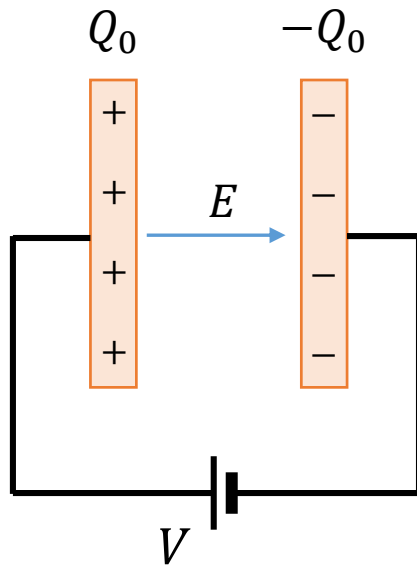
6 Dielectric materials and insulation

陈晓龙 Chen, Xiaolong

电子与电气工程系

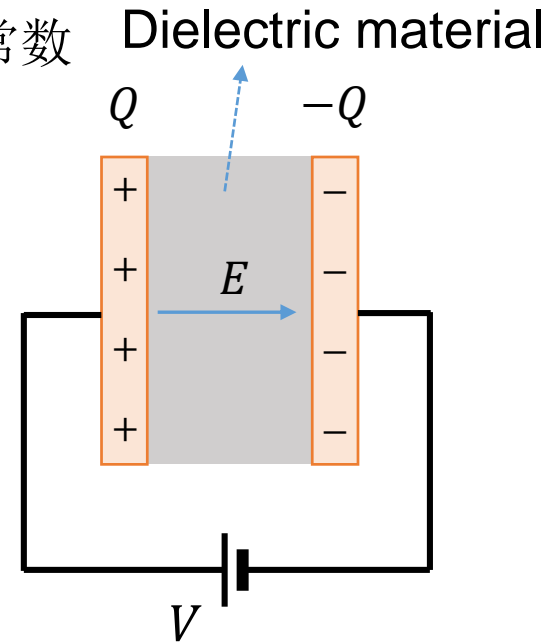
6.1 Matter polarization and relative permittivity

物质极化与相对介电常数



Capacitance of parallel plate capacitor in vacuum:

$$C_0 = Q_0/V$$



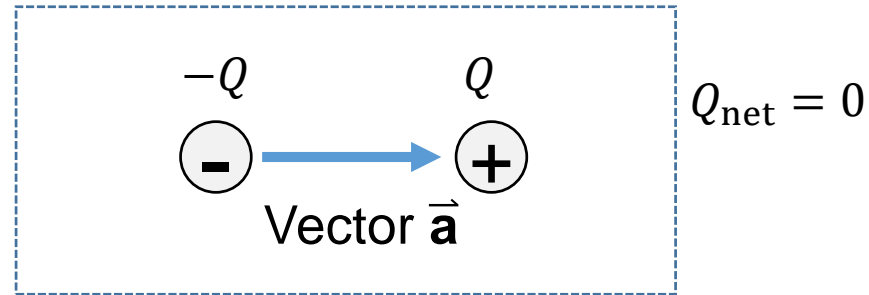
Capacitance of parallel plate capacitor in dielectric material:

$$C = Q/V$$

Relative permittivity/dielectric constant is defined as:

$$\epsilon_r = Q/Q_0$$

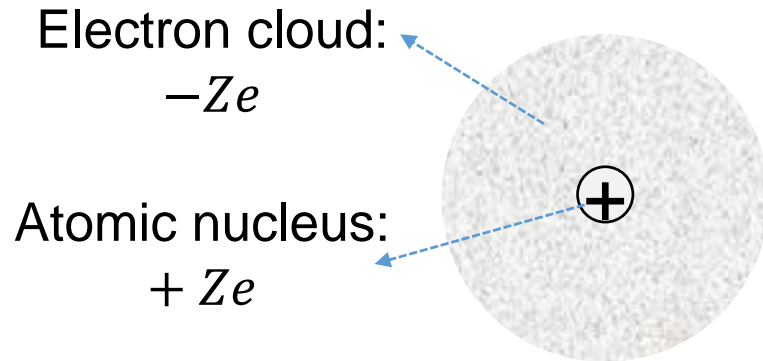
Electric dipole moment 电偶极矩



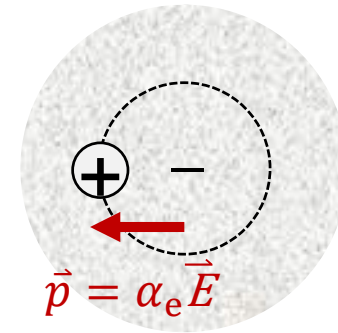
Electric dipole moment: $\vec{p} = Q\vec{a}$

Electric dipole moment in an atom

No electric field: $E=0$

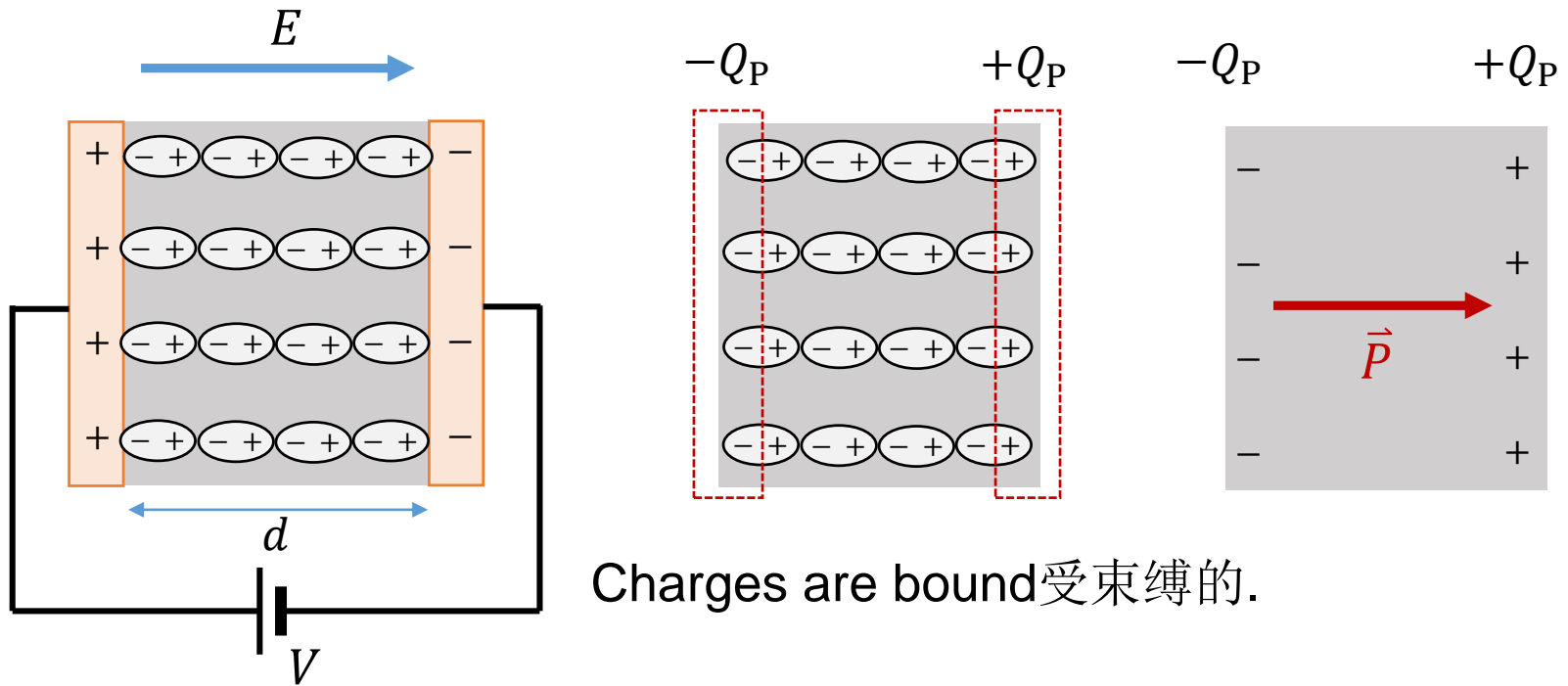


$\leftarrow E$



A dipole is induced: $\vec{p} = \alpha_e \vec{E}$

polarizability 极化率 α_e is called the electronic polarization

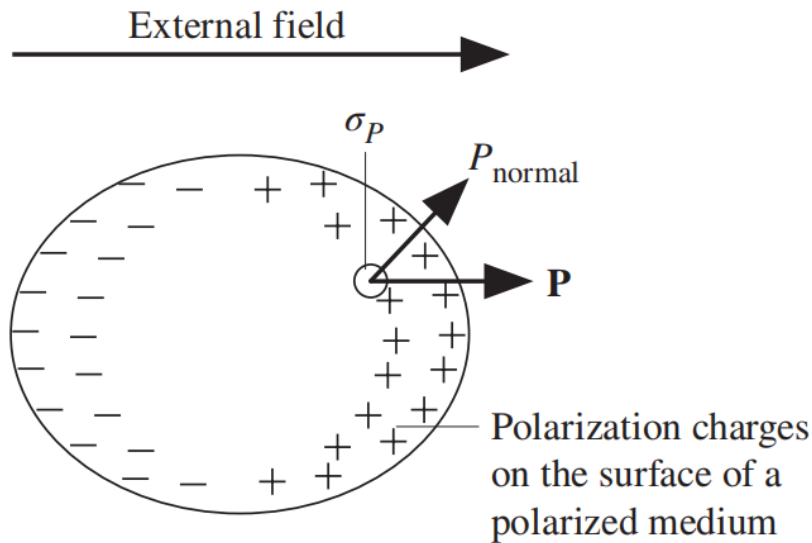


The **polarization vector** of the medium: $\vec{P} = \frac{1}{\text{Volume}} [\vec{p}_1 + \vec{p}_2 + \cdots + \vec{p}_N]$
极化矢量

$$P = \frac{Q_P d}{\text{Volume}} = \frac{Q_P d}{A d} = \frac{Q_P}{A} = \sigma_P$$

Q_P : surface polarization charges

σ_P : surface polarization charge density



$$P_{\text{normal}} = \sigma_P$$

$$P = \chi_e \epsilon_0 E$$

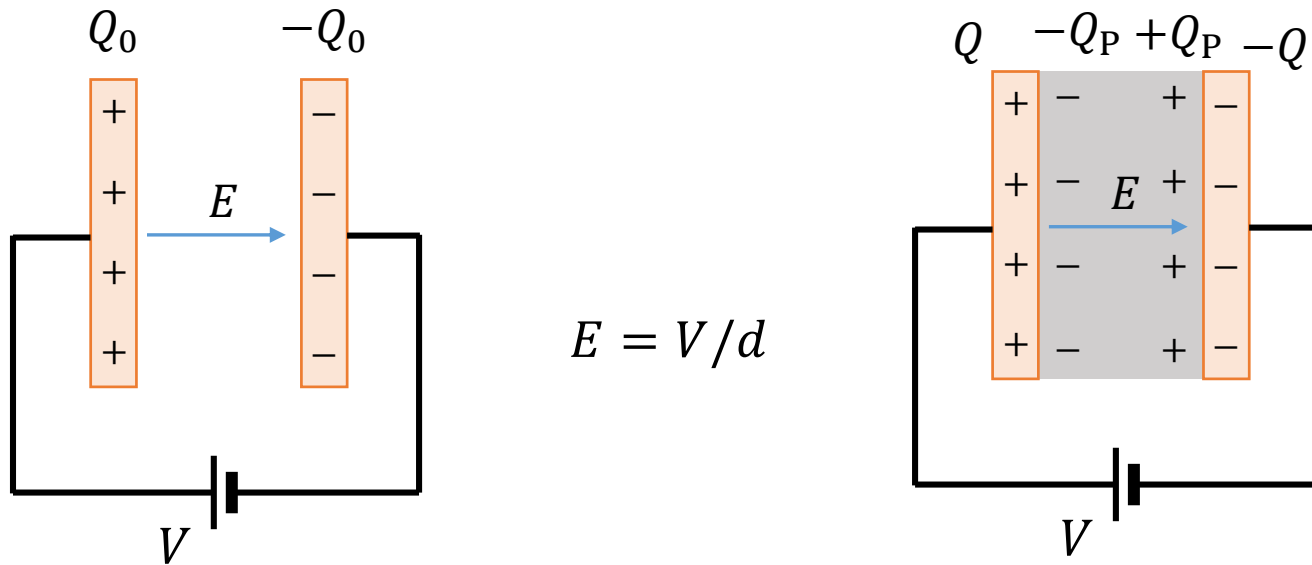
χ_e : electric susceptibility 电极化率

Relation between polarizability α_e and susceptibility χ_e :

$$\left\{ \begin{array}{l} P = \chi_e \epsilon_0 E \\ P = N \alpha_e E \end{array} \right. \quad \Rightarrow \quad \chi_e = \frac{1}{\epsilon_0} N \alpha_e$$

N : number of molecules per unit volume

Relation between relative permittivity and susceptibility χ_e



Because electric field is the same with and without dielectric medium



$$Q_0 = Q - Q_P$$



$$\epsilon_0 E = \sigma - \sigma_P$$

$$\begin{cases} \varepsilon_0 E = \sigma - \sigma_P \\ P = \chi_e \varepsilon_0 E \\ P = \sigma_P \end{cases}$$



$$\sigma = \varepsilon_0(1 + \chi_e)E$$

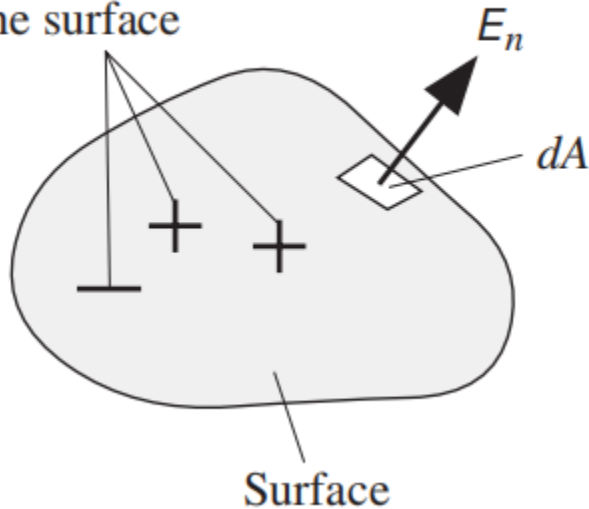


$$\begin{cases} \varepsilon_r = \frac{Q}{Q_0} = \frac{\sigma}{\sigma_0} = 1 + \chi_e \\ \varepsilon_r = 1 + \frac{1}{\varepsilon_0} N \alpha_e \end{cases}$$

$$P = \chi_e \varepsilon_0 E = (\varepsilon_r - 1) \varepsilon_0 E$$

6.2 Gauss's law and boundary conditions

Charges inside
the surface



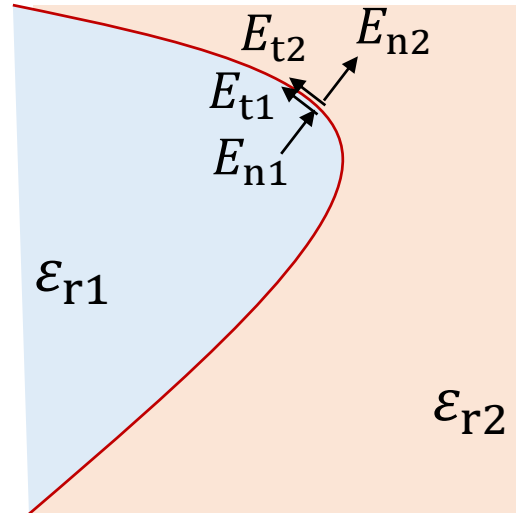
Gauss's law:

$$\oint_{\text{surface}} E_n dA = \frac{Q_{\text{total}}}{\epsilon_0}$$

$$\oint_{\text{surface}} E_n dA = \frac{Q_{\text{free}}}{\epsilon_r \epsilon_0}$$

Total charge Q_{total} : free charges Q_{free} and bound polarization charges.

Boundary conditions



The first boundary condition: $\epsilon_{r1}E_{n1} = \epsilon_{r2}E_{n2}$

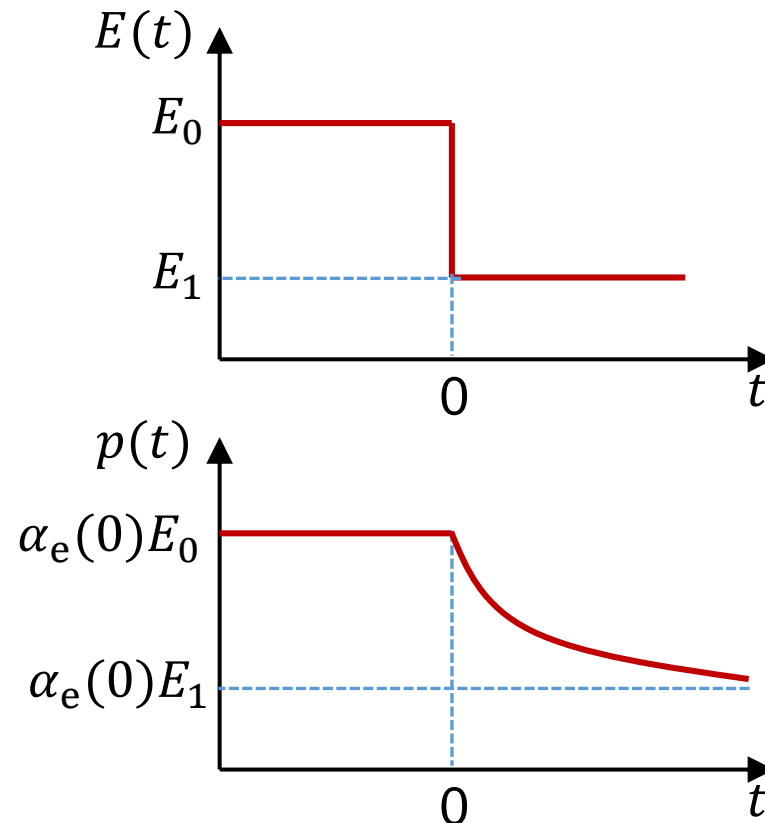
The second boundary condition: $E_{t1} = E_{t2}$

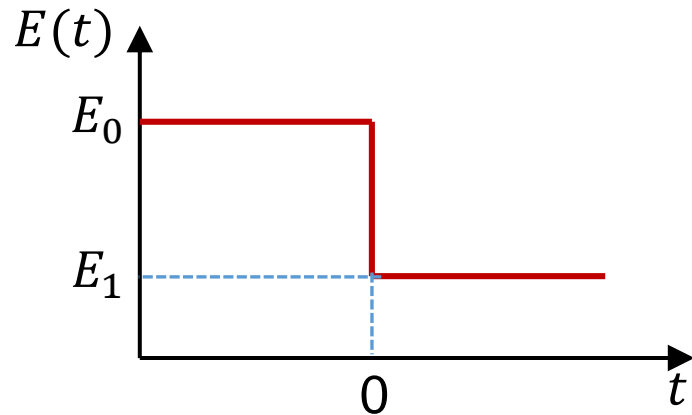
6.3 Frequency dependence: dielectric constant and dielectric loss

Under DC voltage bias ($\omega = 0$), the polarizability is $\alpha_e(0)$.

The dipole moment per molecule: $p = \alpha_e E$.

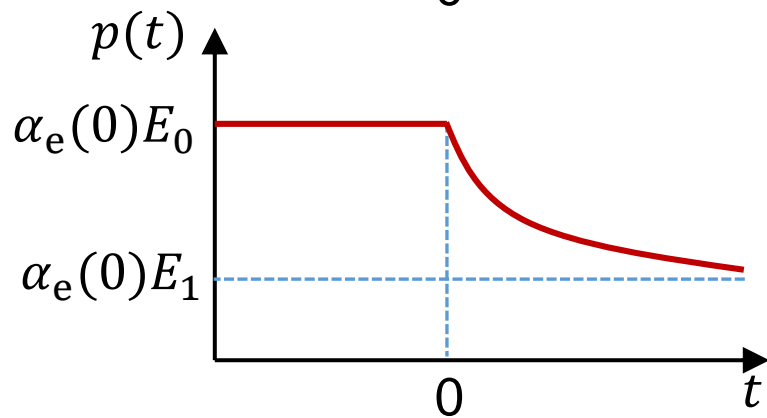
Transient behavior 瞬时行为





Assume τ is the relaxation time, the relaxation equation:

$$\frac{dp}{dt} = -\frac{p - \alpha_e E}{\tau}$$



For AC voltage bias (ω), $E = E_0 \exp(j\omega t)$.

$$\frac{dp}{dt} = -\frac{p}{\tau} + \frac{\alpha_e(0)}{\tau} E_0 \exp(j\omega t)$$



$$\left\{ \begin{array}{l} p = \alpha_e(\omega) E_0 \exp(j\omega t) \\ \alpha_e(\omega) = \frac{\alpha_e(0)}{1 + j\omega\tau} \end{array} \right.$$

Complex dielectric constant

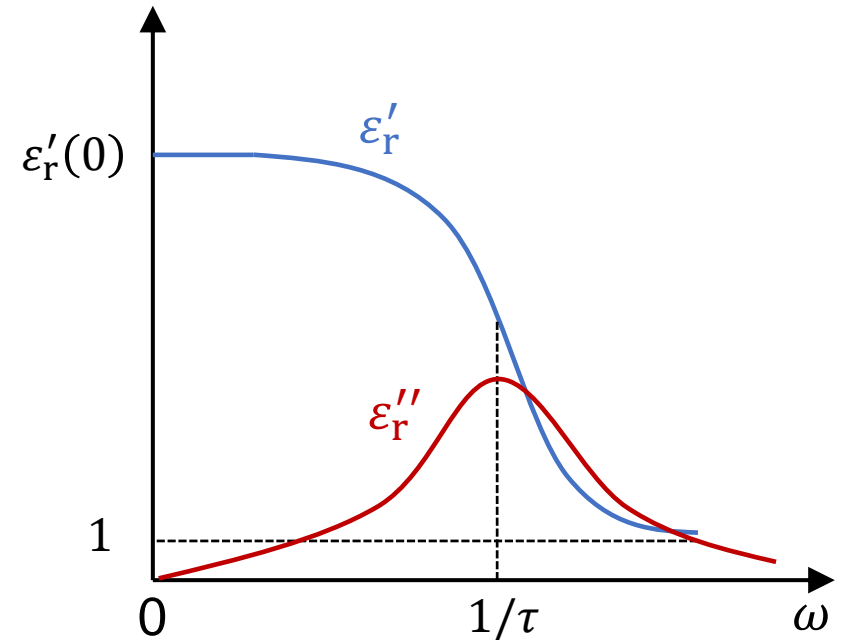
$$\varepsilon_r(\omega) = 1 + \frac{1}{\varepsilon_0} N \alpha_e(\omega)$$

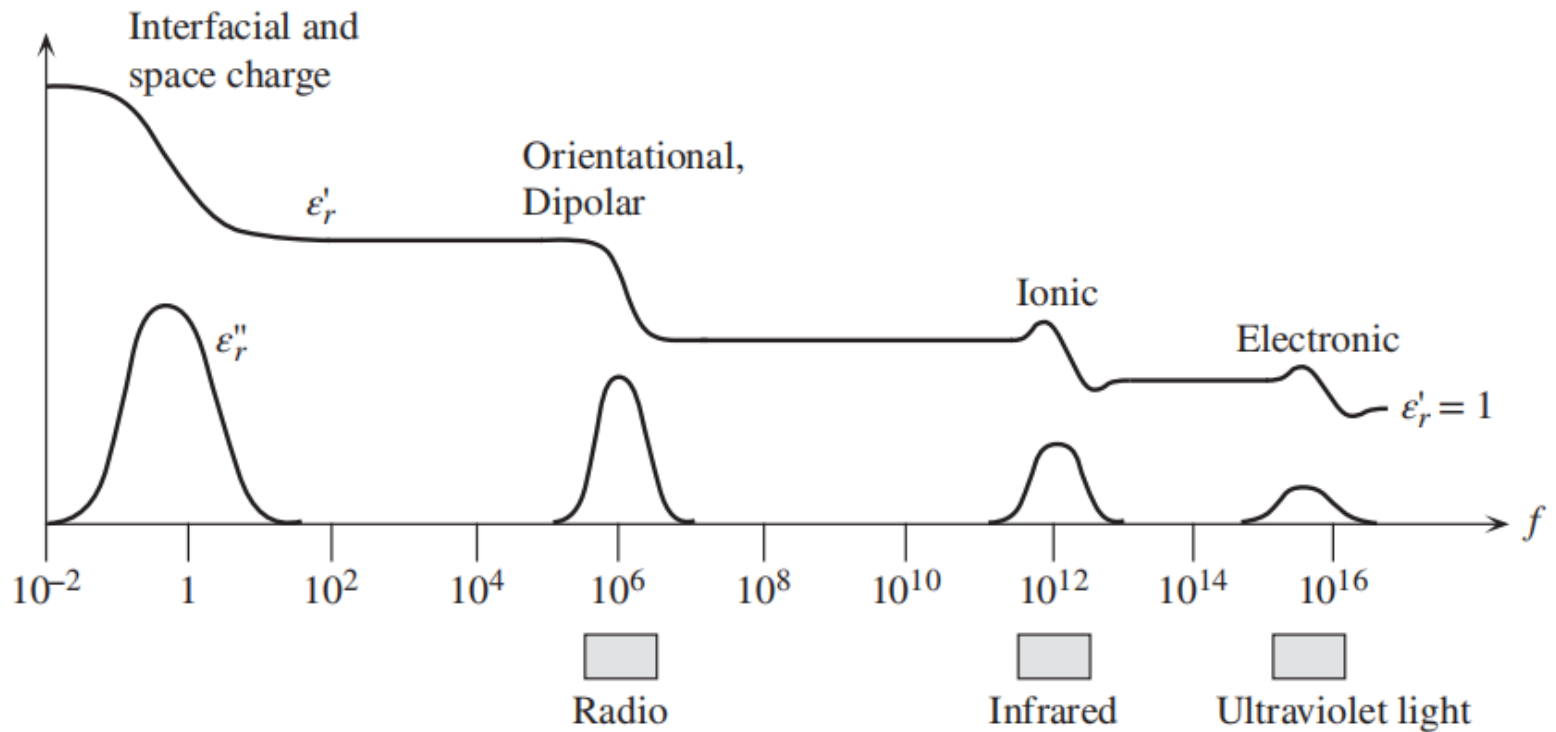


$$\varepsilon_r(\omega) = 1 + \frac{1}{\varepsilon_0} N \frac{\alpha_e(0)}{1 + j\omega\tau}$$



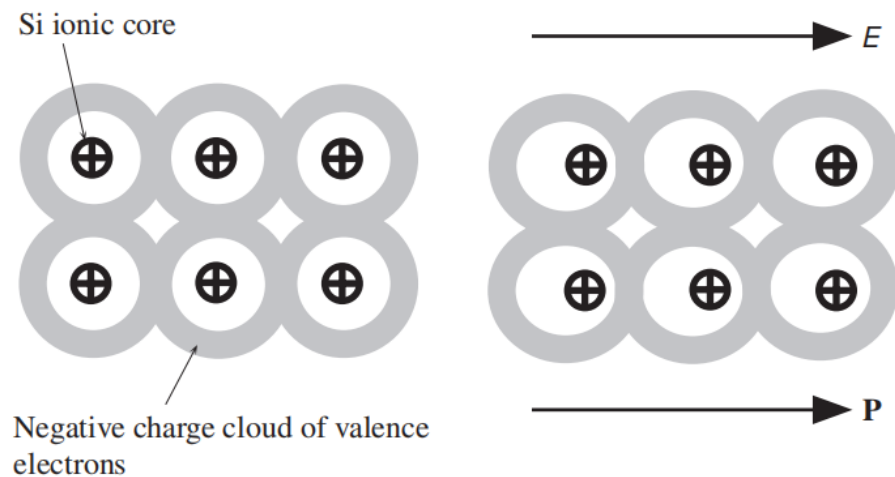
$$\left\{ \begin{array}{l} \varepsilon_r(\omega) = \varepsilon_r'(\omega) - j\varepsilon_r''(\omega) \\ \varepsilon_r'(\omega) = 1 + \frac{N}{\varepsilon_0(1 + \omega^2\tau^2)} \alpha_e(0) \\ \varepsilon_r''(\omega) = \frac{N\omega\tau}{\varepsilon_0(1 + \omega^2\tau^2)} \alpha_e(0) \end{array} \right.$$

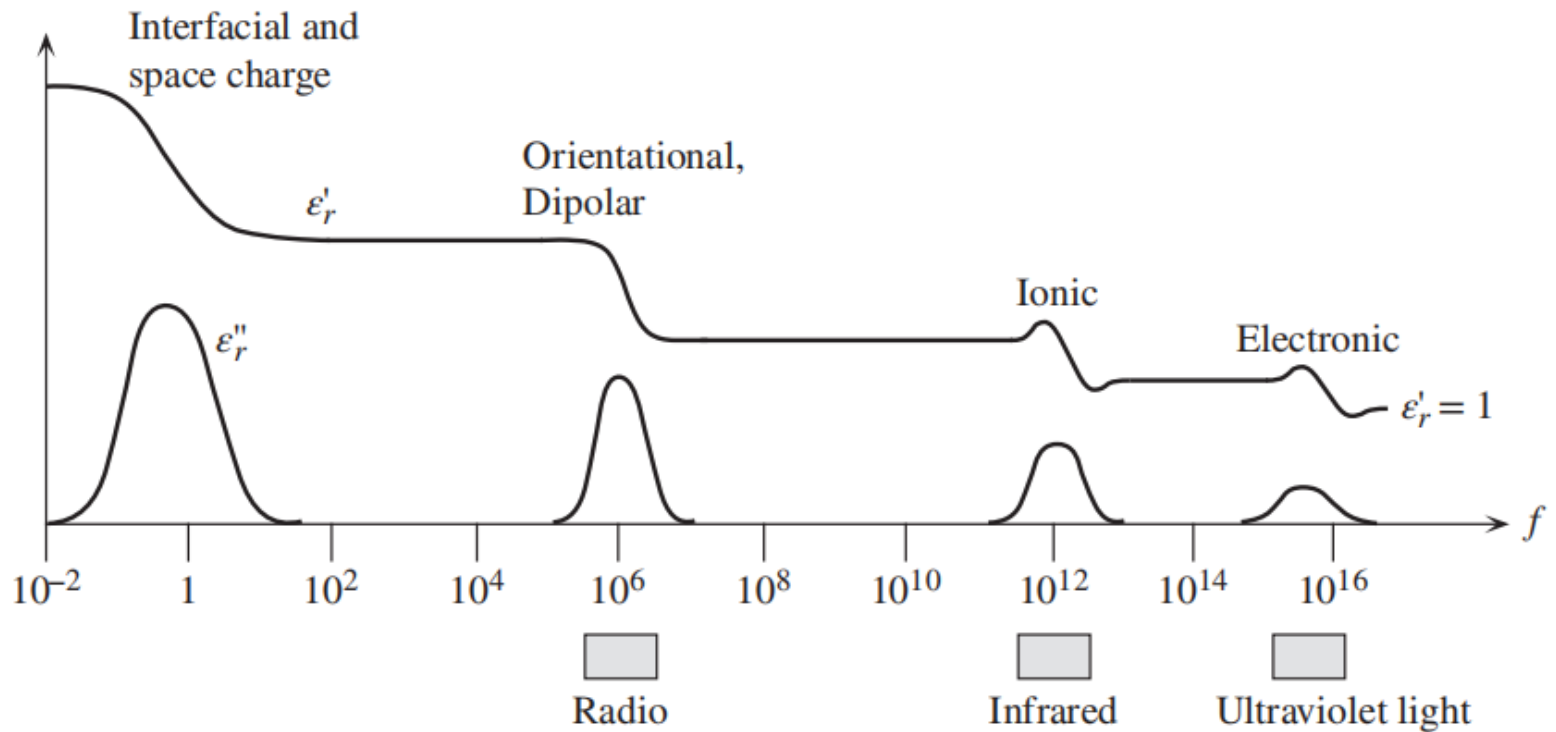




Electronic polarization

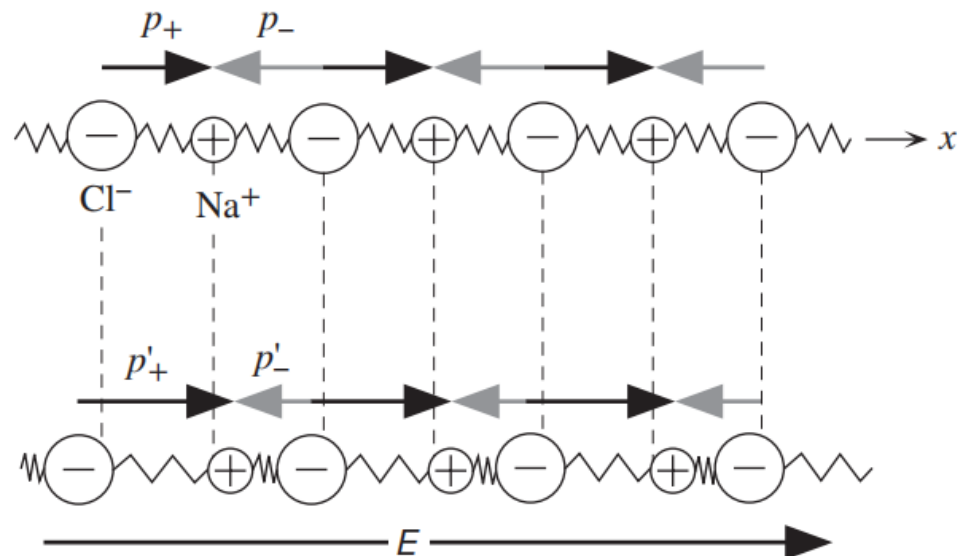
For covalent bond solids

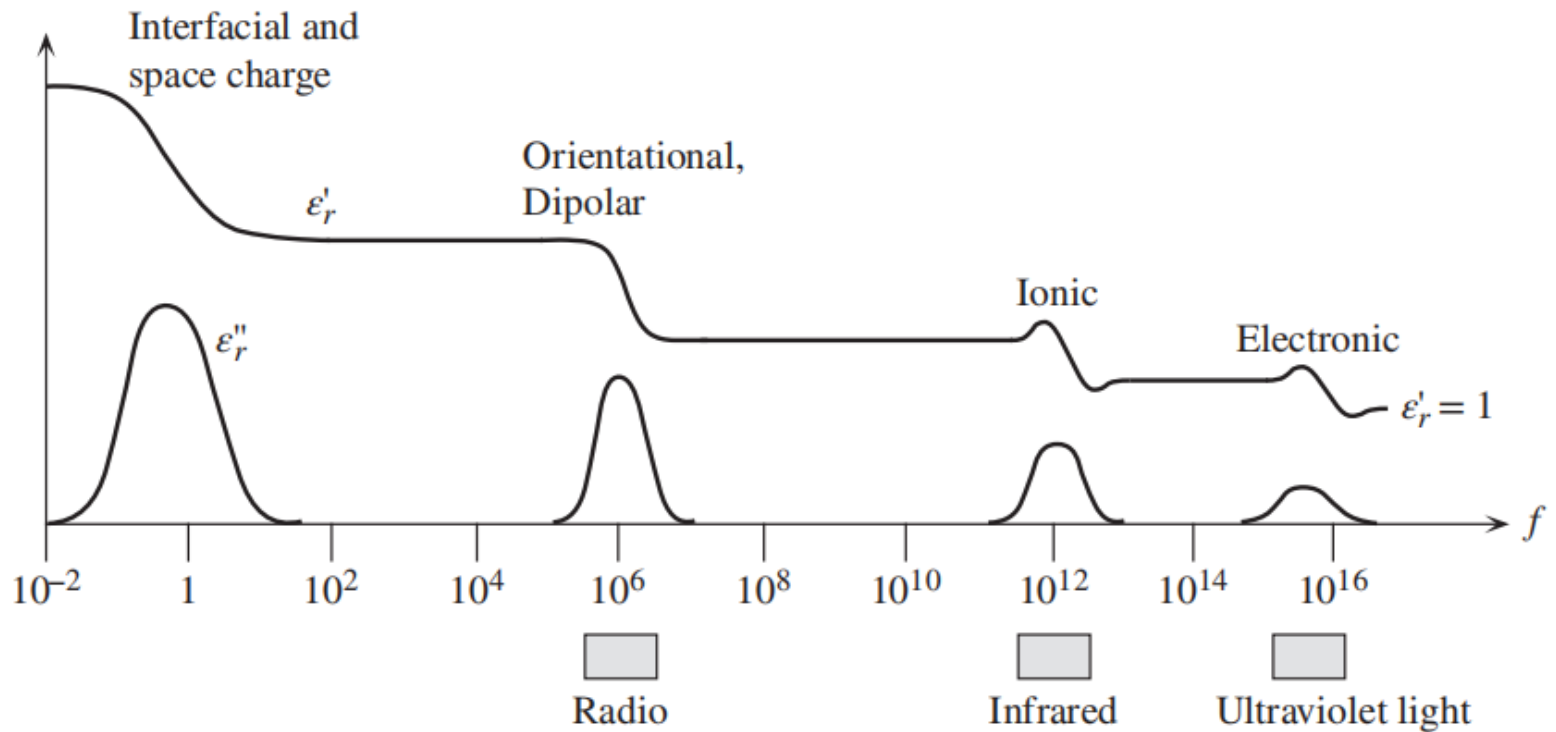




Ionic
polarization

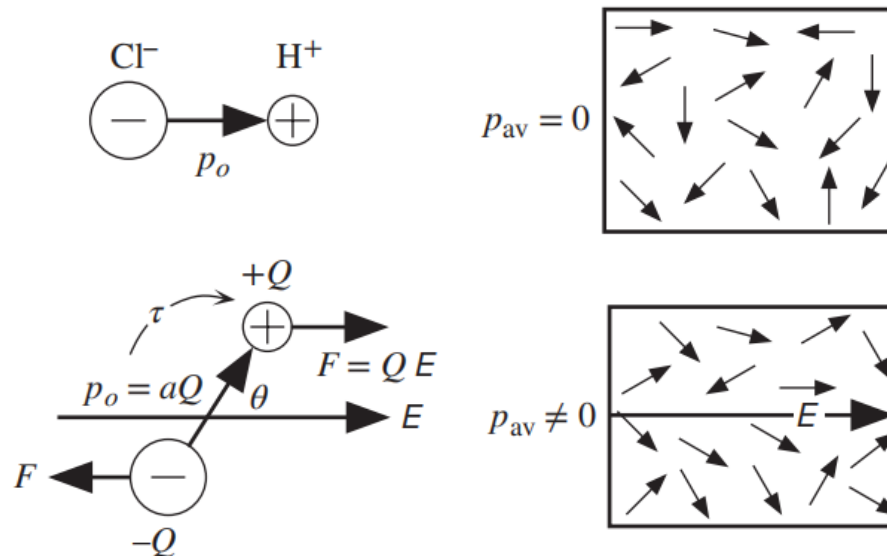
$$p = \alpha_i E$$

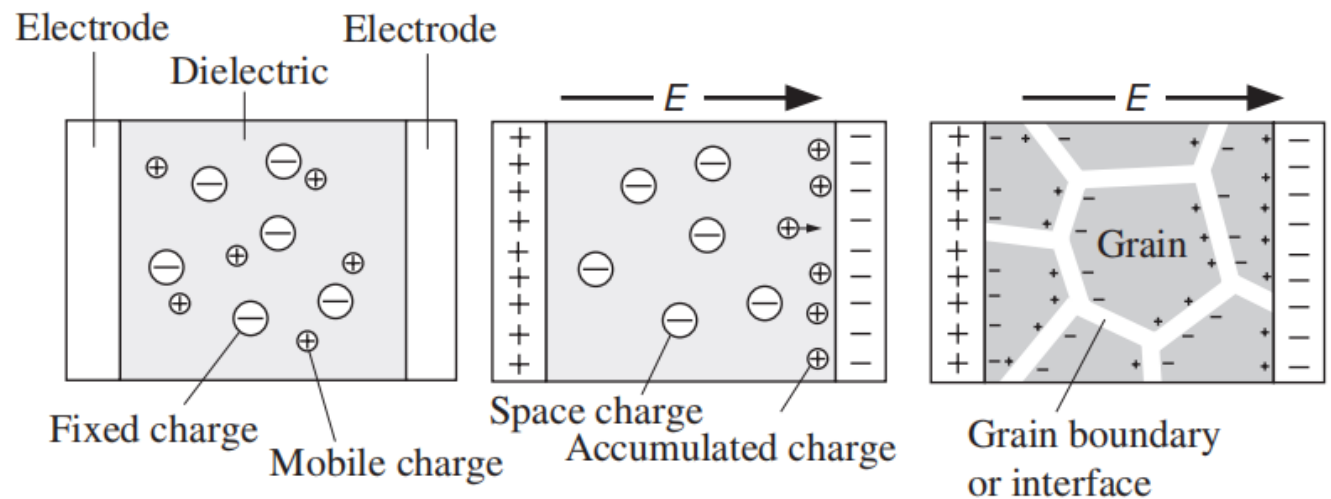
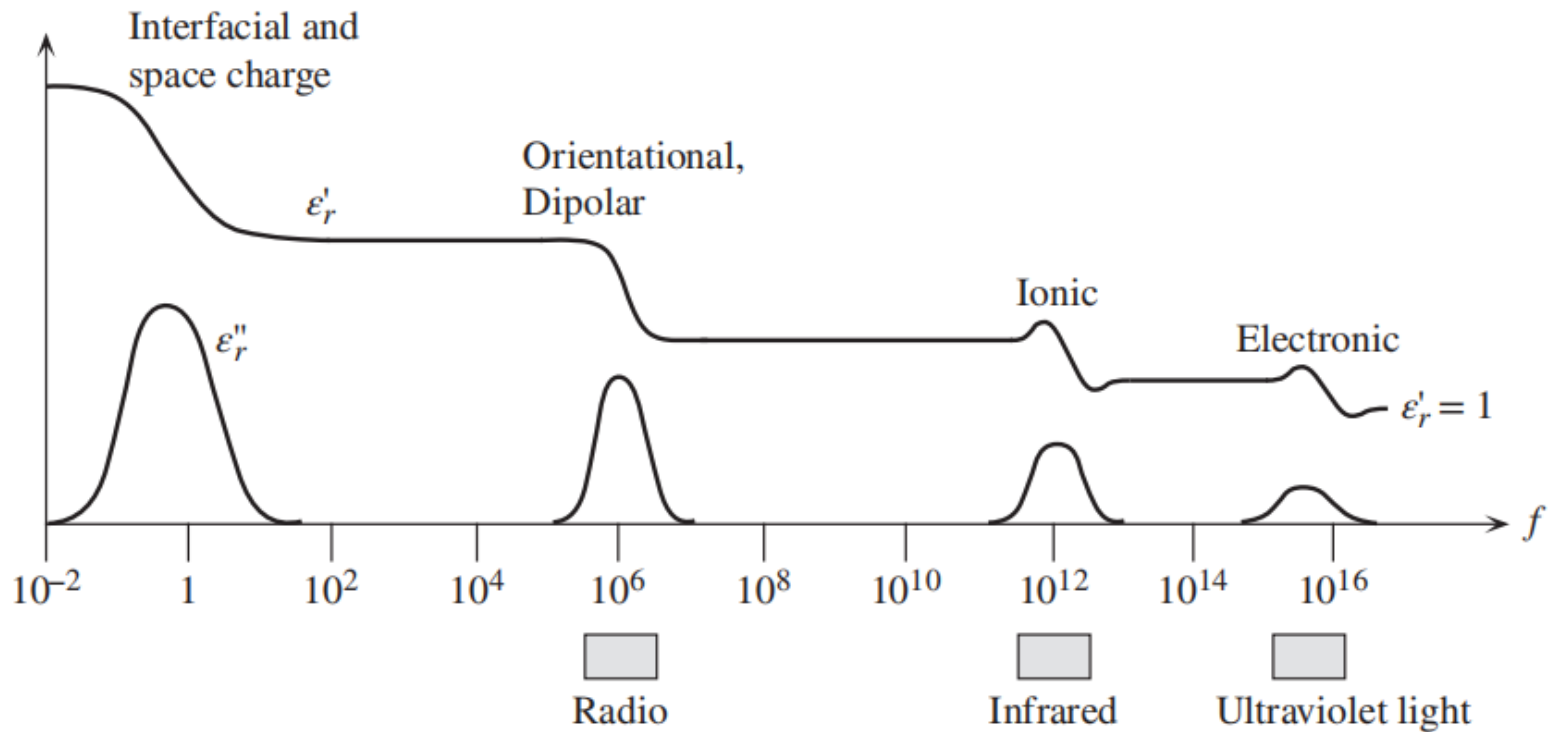




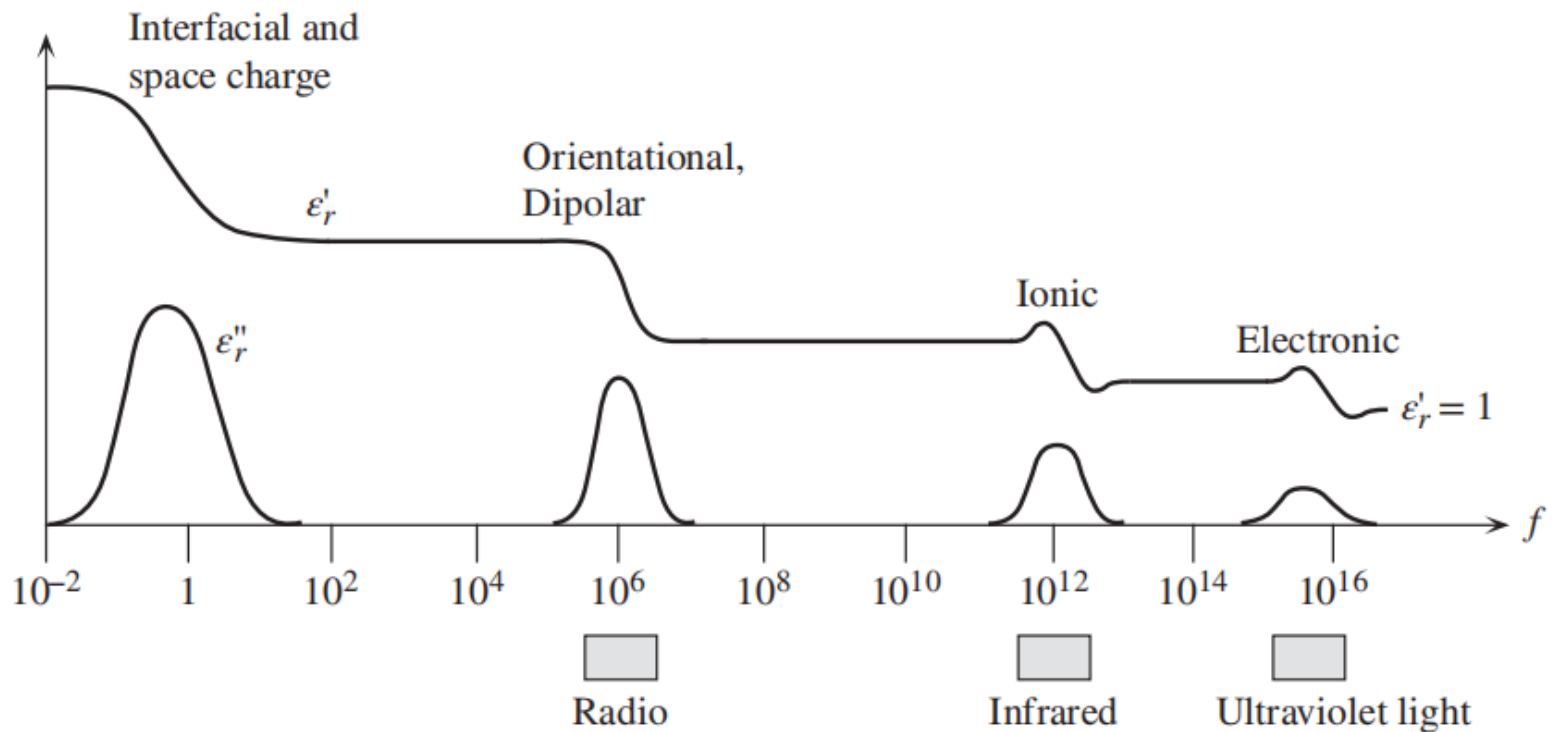
Orientational polarization

$$p = \alpha_d E$$





Interfacial and
space charge

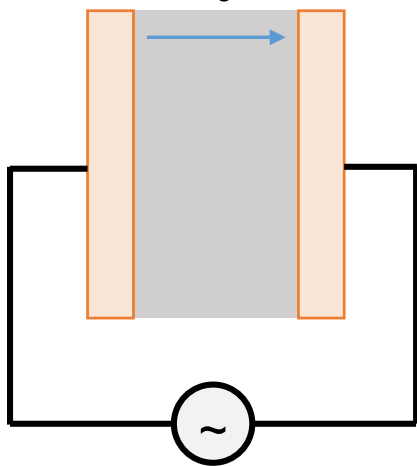


The total dipole moment of per molecule is the sum of all contributions.

Admittance of capacitor 电容的导纳

$$P = P_0 \sin(\omega t - \phi)$$

$$E = E_0 \sin \omega t$$



$$v = V_0 \sin \omega t$$

$$C = \frac{A \epsilon_0 \epsilon_r(\omega)}{d}$$

Admittance of capacitor Y :

Impedance of capacitor X :

$$Y = \frac{1}{X} = j\omega C$$

$$Y = \frac{j\omega A \epsilon_0 \epsilon_r(\omega)}{d}$$

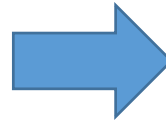
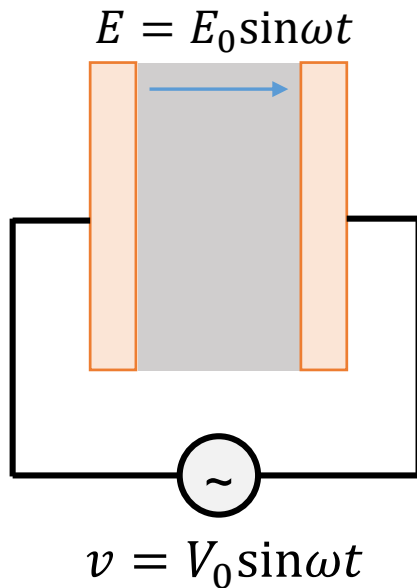
$$Y = \frac{j\omega A \epsilon_0 \epsilon_r'(\omega)}{d} + \frac{\omega A \epsilon_0 \epsilon_r''(\omega)}{d}$$

$$= j\omega C' + G_P$$

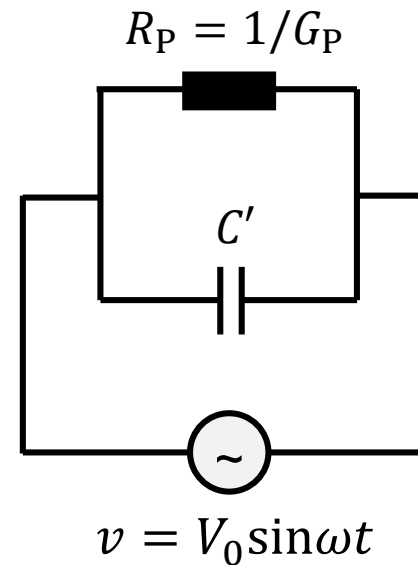
$$C' = \frac{A \epsilon_0 \epsilon_r'(\omega)}{d}, \quad G_P = \frac{\omega A \epsilon_0 \epsilon_r''(\omega)}{d}$$

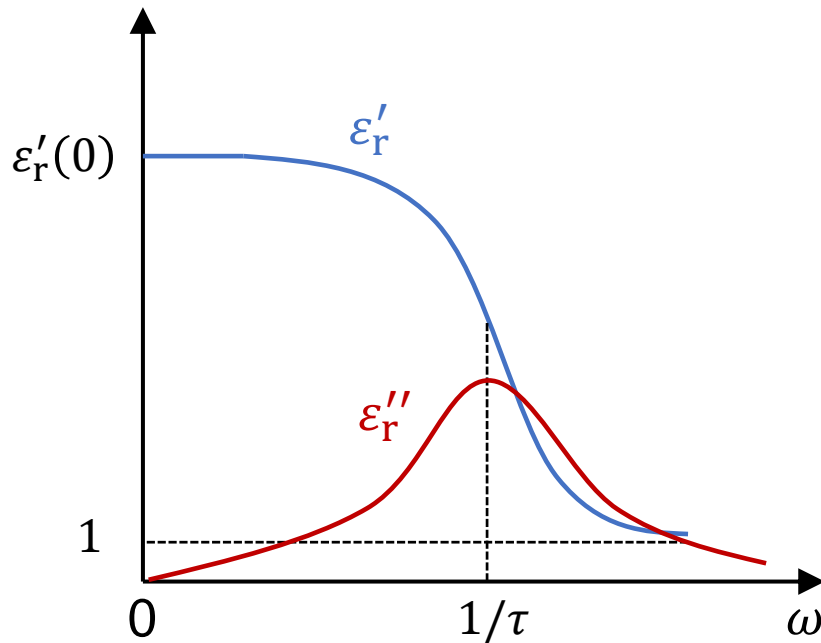
Admittance of capacitor: $Y = j\omega C' + G_P$

$$P = P_0 \sin(\omega t - \phi)$$



Equivalent circuit





Input power:

$$IV = YV^2$$

$$= j\omega C'V^2 + G_P V^2$$

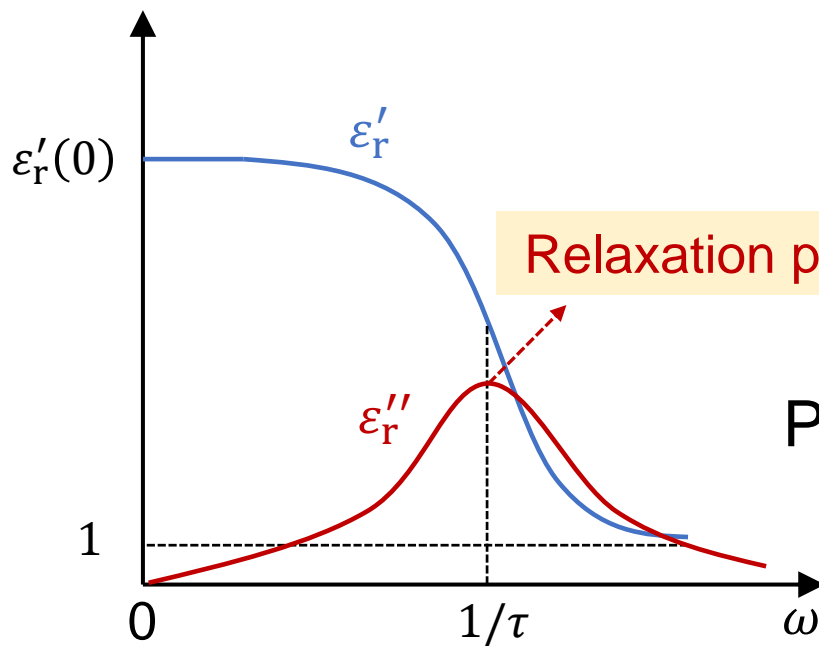
$$= j\omega C'V^2 + \frac{V^2}{R_P}$$

$$\left\{ \begin{array}{l} C' = \frac{A\epsilon_0\epsilon'_r(\omega)}{d} \\ G_P = \frac{\omega A\epsilon_0\epsilon''_r(\omega)}{d} \end{array} \right.$$

The imaginary term:

Power stored in capacitor C'

No power is dissipated in C'



Input power: $j\omega C'V^2 + \frac{V^2}{R_P}$

The real term:

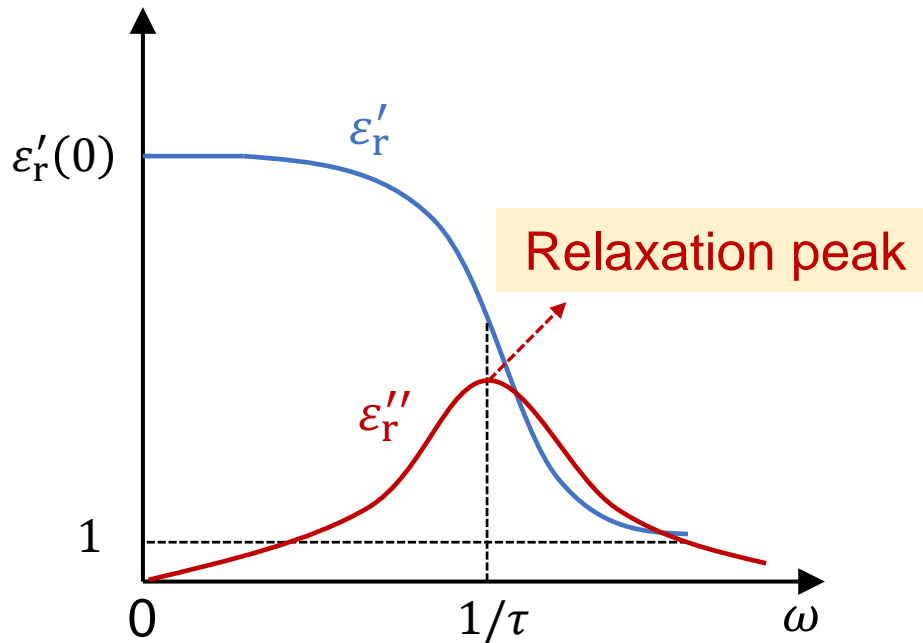
Power dissipated in dielectric medium

Power dissipation reaches the maximum value at $\omega = 1/\tau$

$$\left\{ \begin{array}{l} C' = \frac{A\epsilon_0\epsilon'_r(\omega)}{d} \\ G_P = \frac{\omega A\epsilon_0\epsilon''_r(\omega)}{d} \end{array} \right.$$

At $\omega = 1/\tau$, most energy is transferred to heat with a high efficiency.

This process is called **dielectric resonance** 介电谐振.



Input power: $j\omega C'V^2 + \frac{V^2}{R_P}$

Energy stored: $\omega C'V^2$

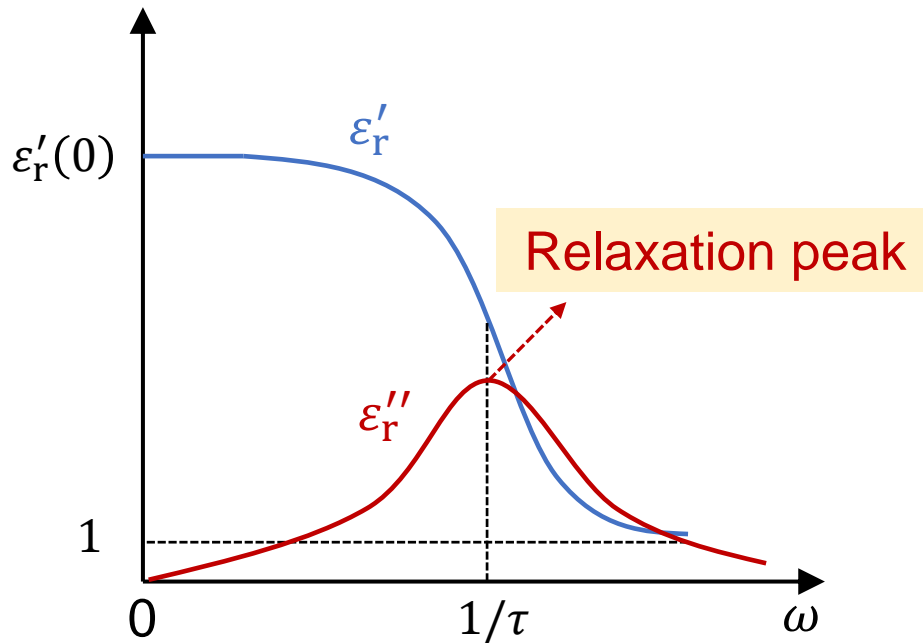
Energy dissipated: $G_P V^2$

Loss tangent (loss factor)

损耗角正切

$$\left\{ \begin{array}{l} C' = \frac{A\epsilon_0\epsilon'_r(\omega)}{d} \\ G_P = \frac{\omega A\epsilon_0\epsilon''_r(\omega)}{d} \end{array} \right.$$

$$\tan\delta = \frac{G_P V^2}{\omega C' V^2} = \frac{\epsilon''_r}{\epsilon'_r}$$



Energy dissipated per unit volume:

$$W_{\text{vol}} = \frac{\text{Power loss}}{\text{Volume}}$$

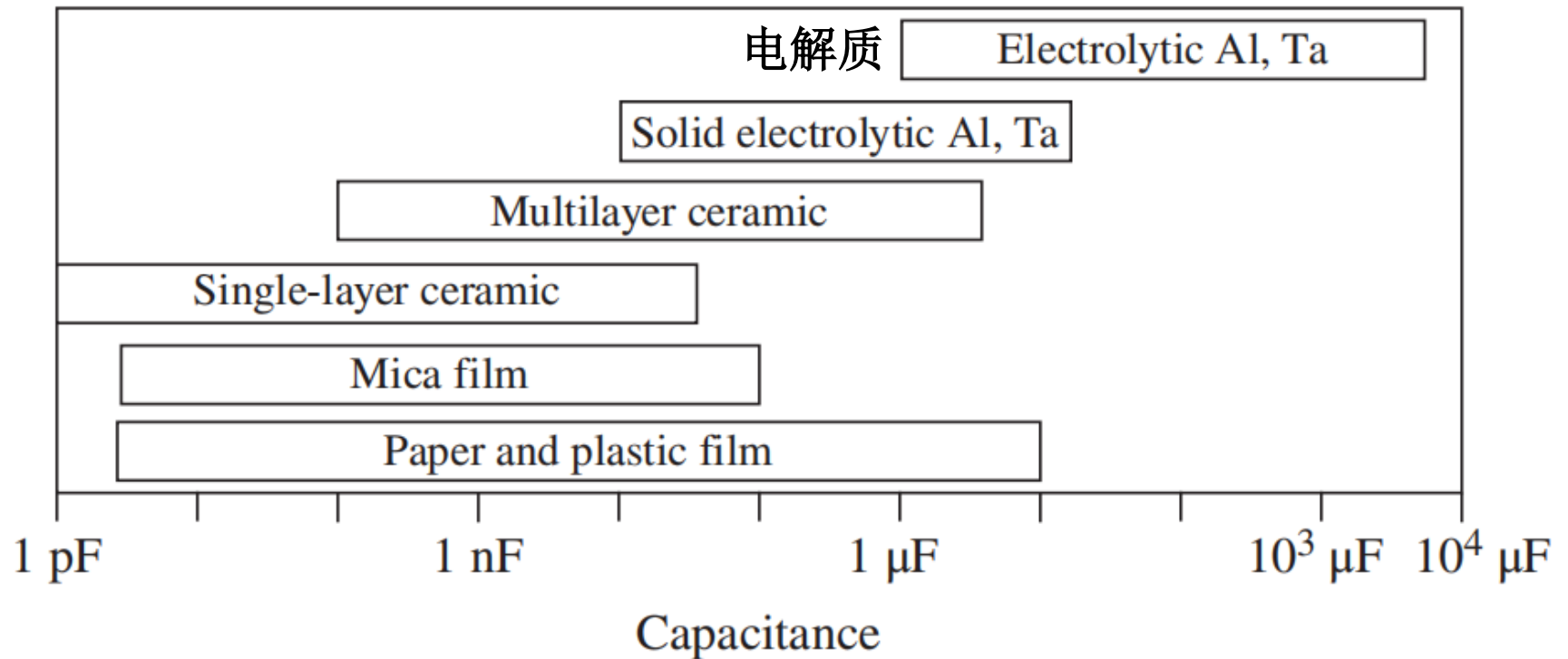
$$= \frac{V^2}{R_P} \times \frac{1}{dA}$$

$$= \frac{V^2}{d^2} \omega \epsilon_0 \epsilon''_r$$

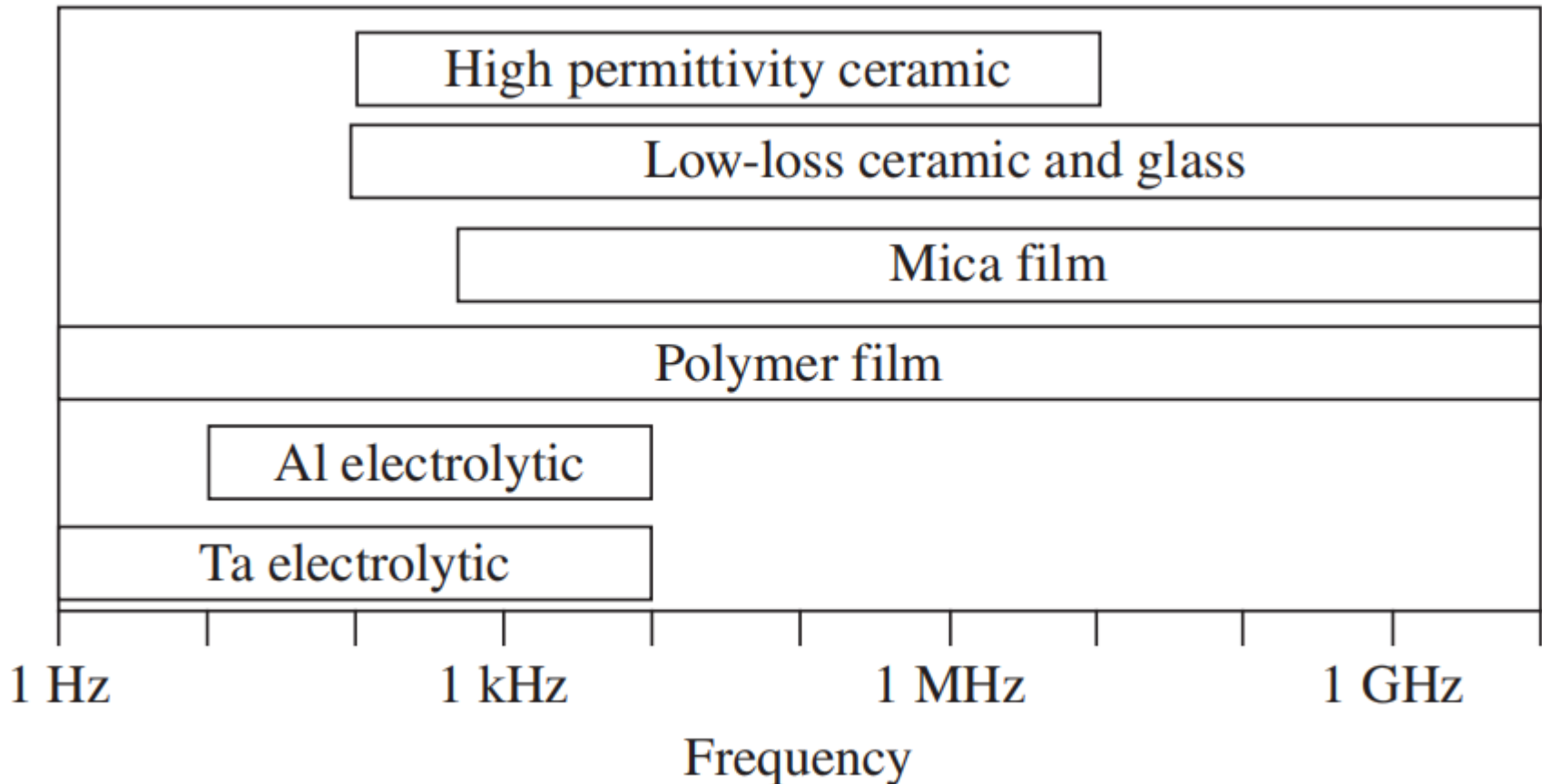
$$= \omega E^2 \epsilon_0 \epsilon'_r \tan \delta$$

$$\left\{ \begin{array}{l} C' = \frac{A \epsilon_0 \epsilon'_r(\omega)}{d} \\ G_P = \frac{\omega A \epsilon_0 \epsilon''_r(\omega)}{d} \end{array} \right.$$

6.4 Capacitor dielectric materials

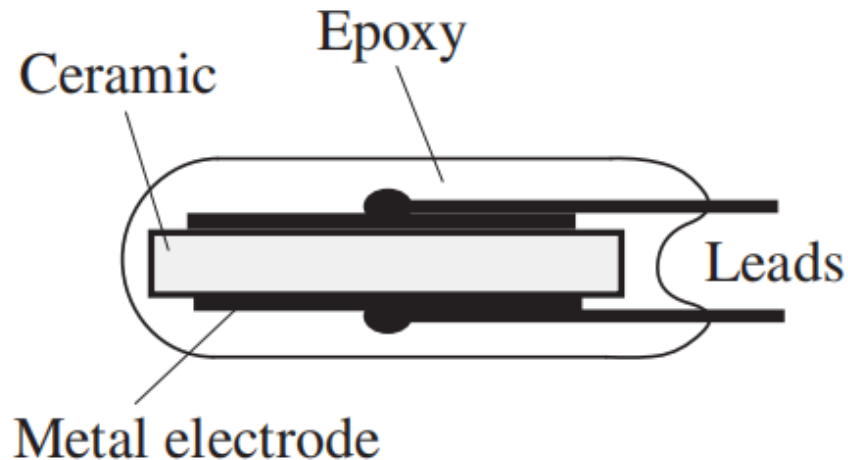


Energy dissipated per unit volume: $W_{\text{vol}} = \omega E^2 \epsilon_0 \epsilon_r' \tan \delta$



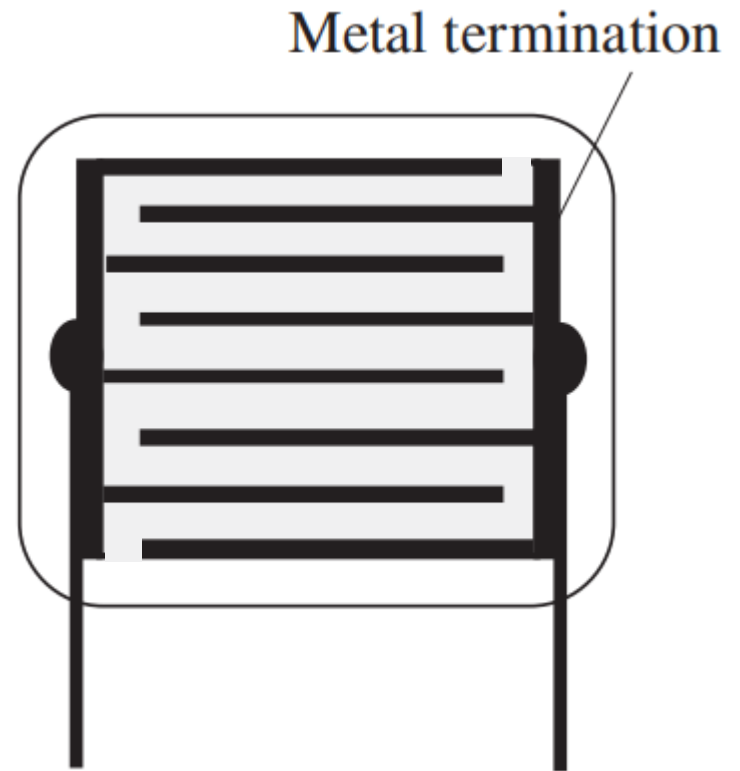
Ceramic parallel-plate capacitor 平行板陶瓷电容器

Single-layer ceramic capacitor

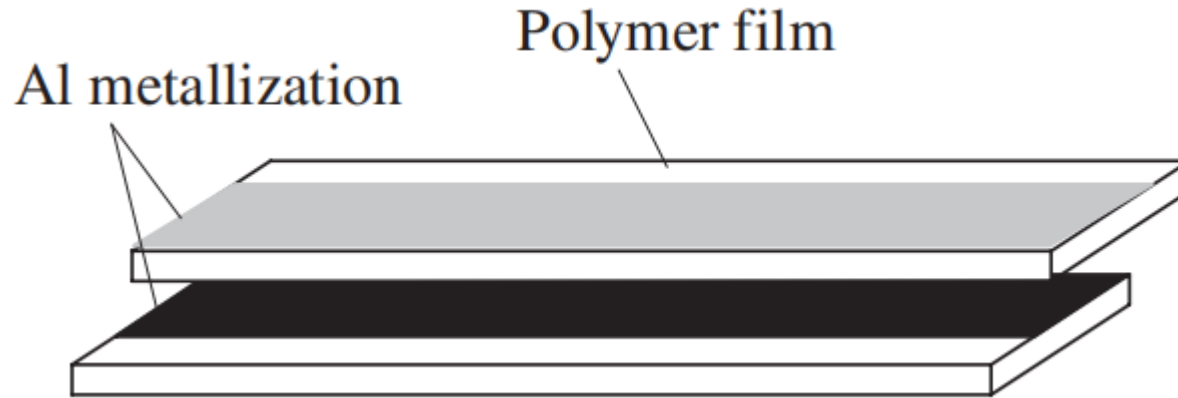


$$C = \frac{A\epsilon_0\epsilon_r(\omega)}{d}$$

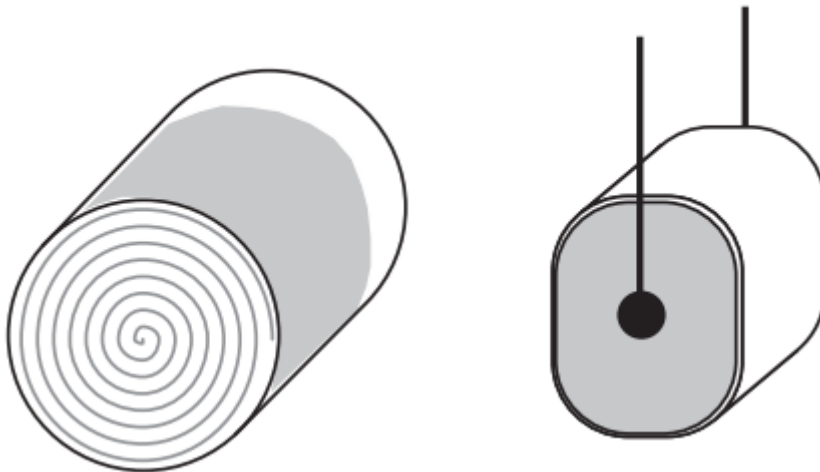
Multilayer ceramic capacitor



Polymer tape capacitor

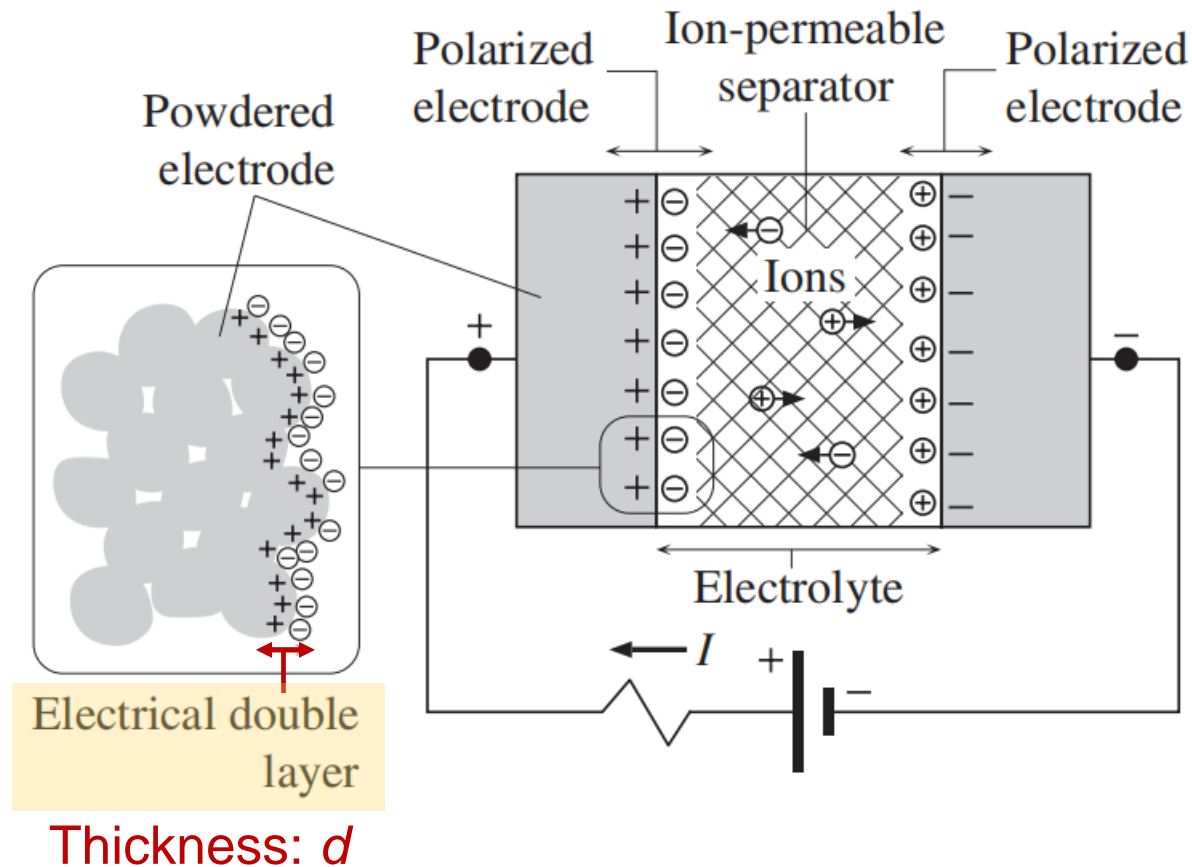


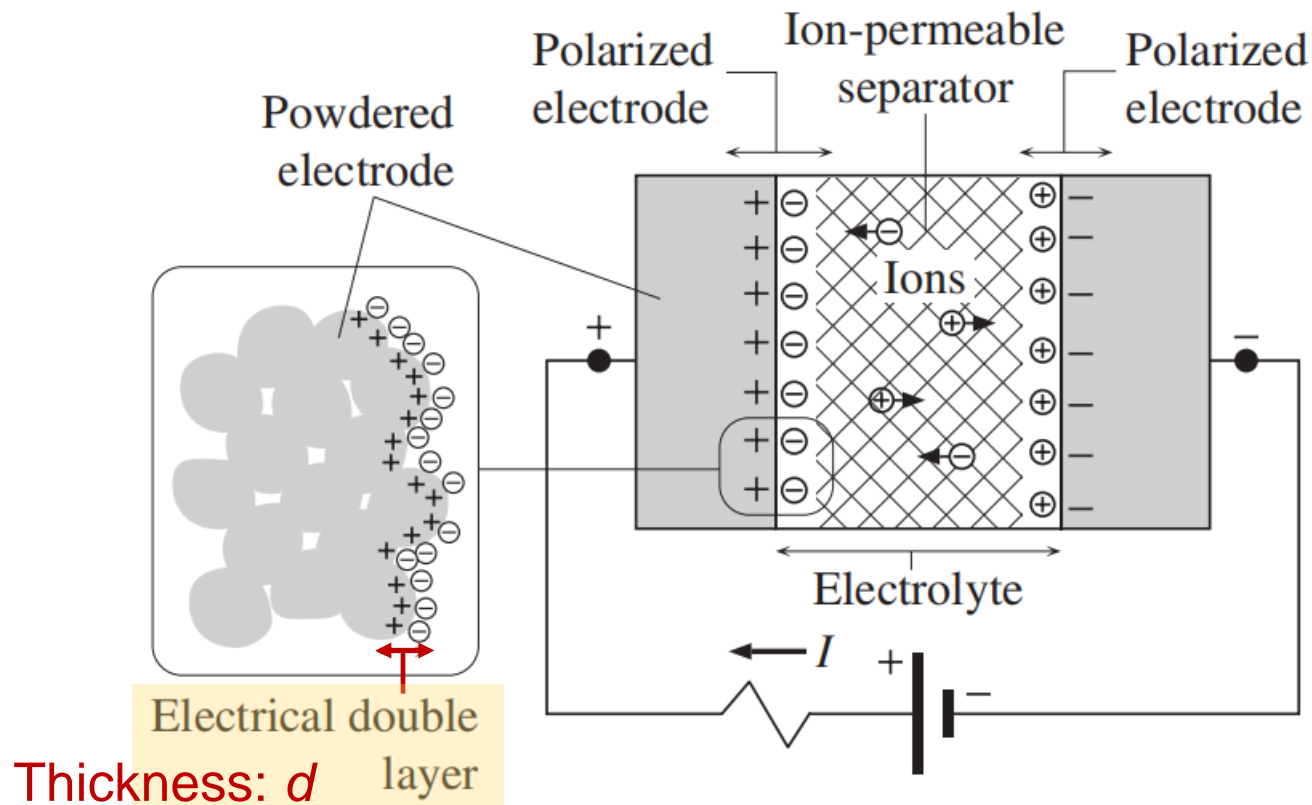
Since polymer tapes are flexible, the capacitor can be rolled together



Supercapacitors 超级电容器

Capacitance is as high as 100 F or more



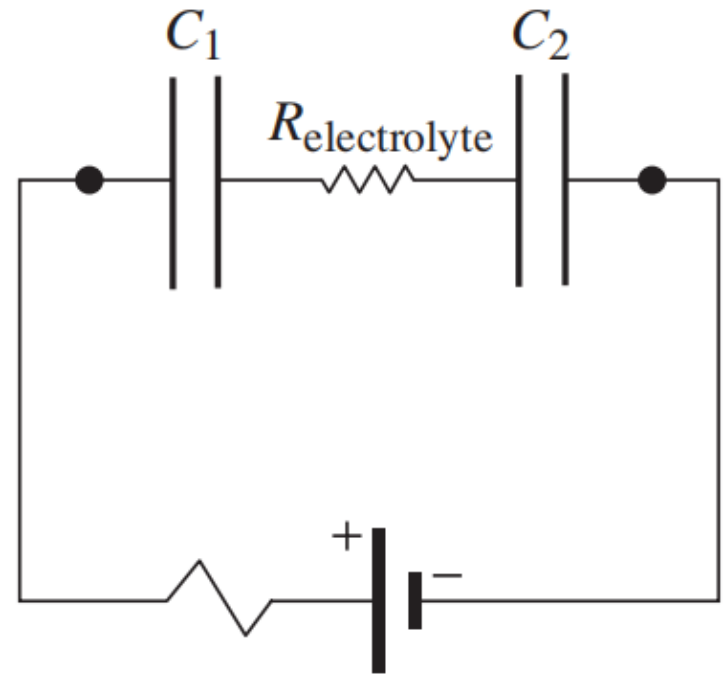
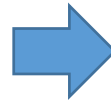
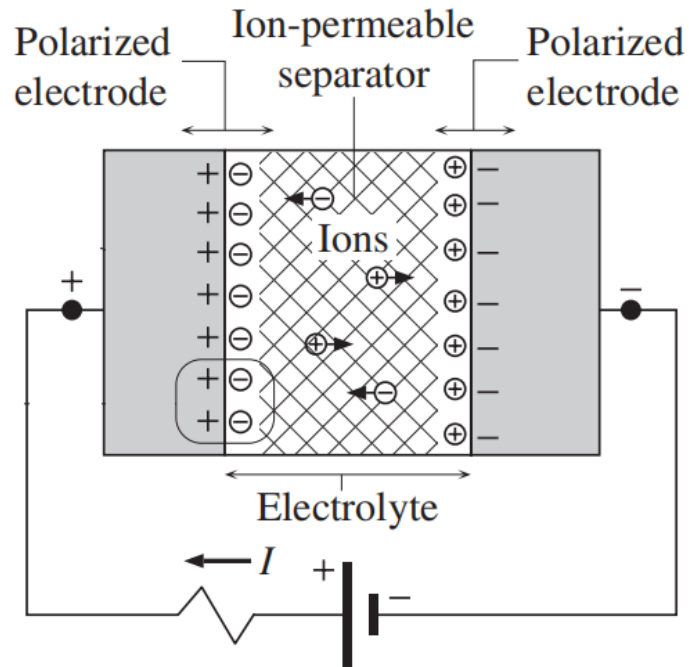


Electrolyte should not react with electrode.

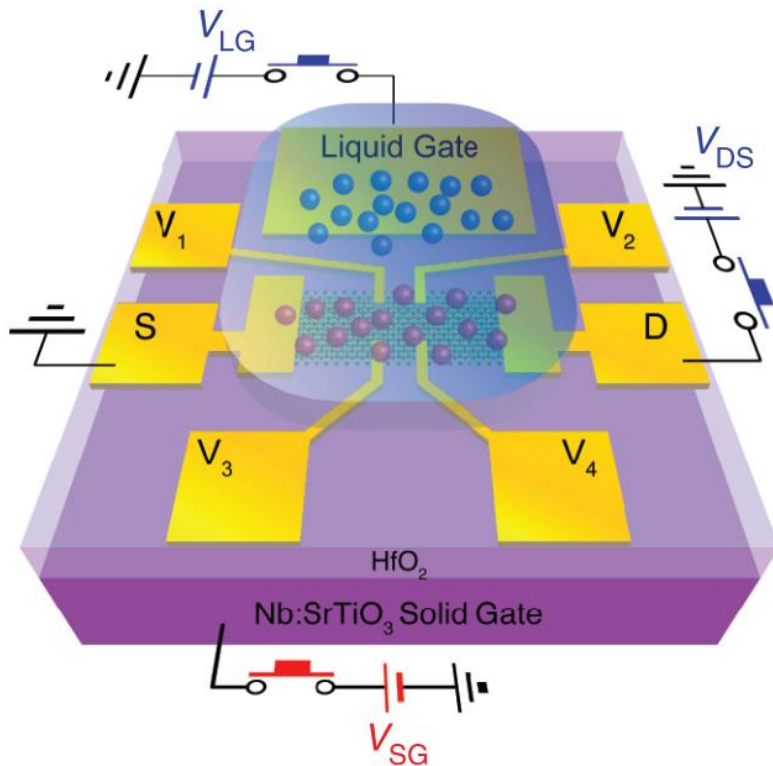
Separation between electrical double layer is $< 1\text{nm}$

$$C = \frac{A\epsilon_0\epsilon_r(\omega)}{d}$$

Equivalent circuit



Electrolyte can use as gate electrode for transistors



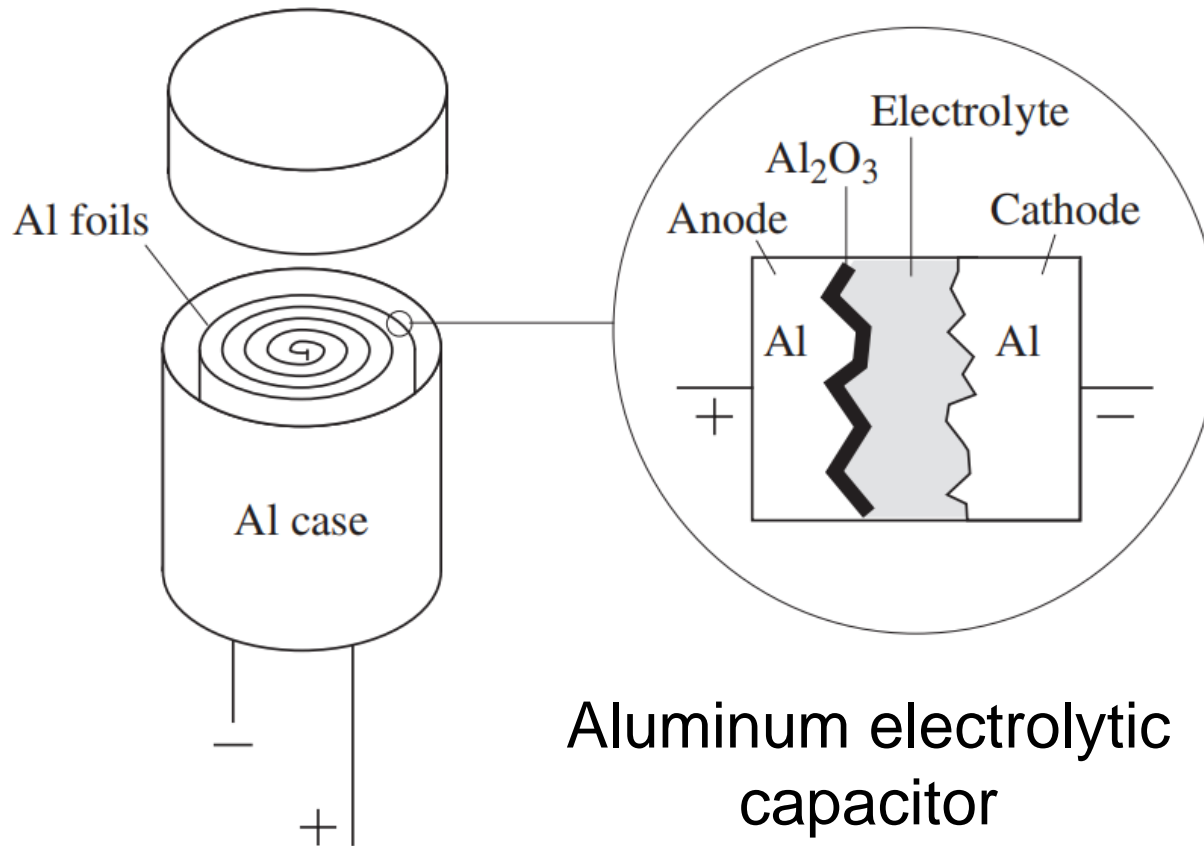
Merits:

- ◆ Very large gate capacitance
- ◆ Can effectively tune the Fermi energy of the channel material
- ◆ Can even tune the Fermi energy of metallic materials

Drawbacks:

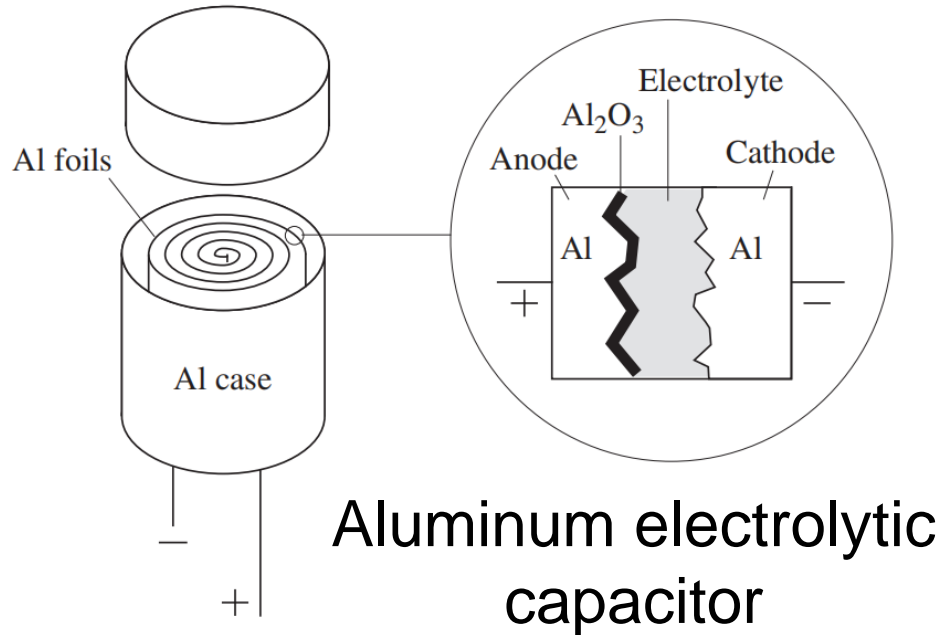
- ◆ Slow response speed

Electrolytic capacitors 电解电容器



Dielectric material is a thin layer of Al_2O_3 (~100 nm)

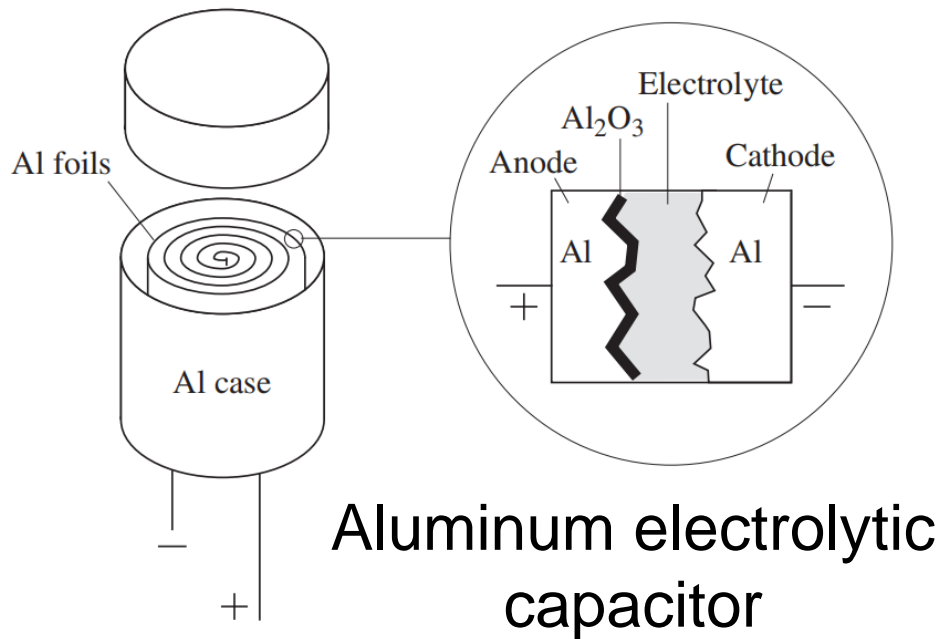
Electrolytic capacitors 电解电容器



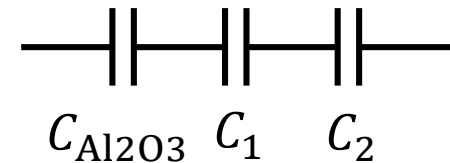
- ◆ Positive voltage on anode: behave as capacitor
- ◆ Negative voltage on anode: conducting

Behave as a rectifier

Electrolytic capacitors 电解电容器



Capacitance:



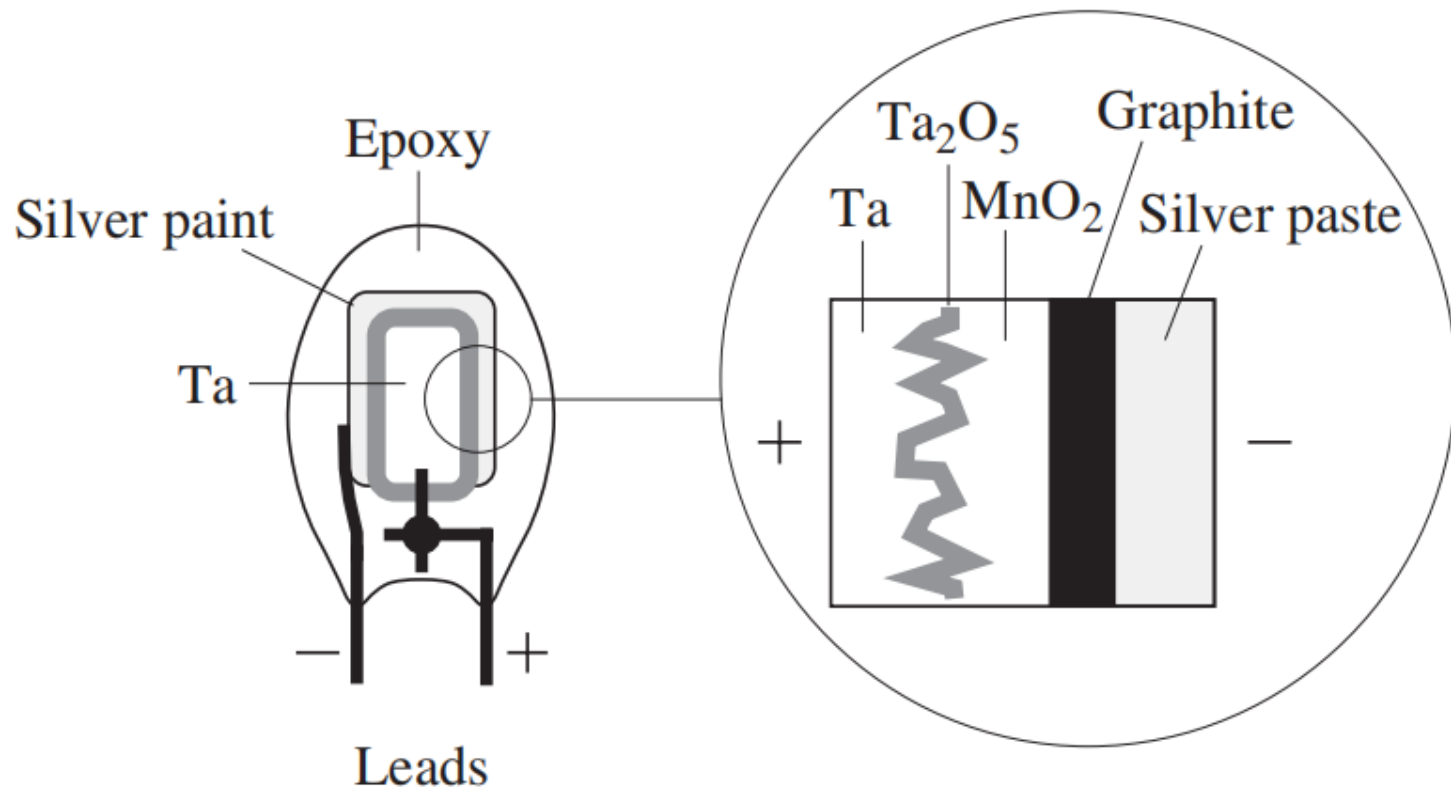
$$C_{\text{Al}_2\text{O}_3} = \frac{A_1 \epsilon_0 \epsilon_{r_ \text{Al}_2\text{O}_3}}{d_{\text{Al}_2\text{O}_3}}$$

$$C_1 = \frac{A_1 \epsilon_0 \epsilon_{r_ \text{Eletro}}}{d_{\text{DL}}}$$

$$C_2 = \frac{A_2 \epsilon_0 \epsilon_{r_ \text{Eletro}}}{d_{\text{DL}}}$$

Total capacitance: $C = C_{\text{Al}_2\text{O}_3} || C_1 || C_2 \approx C_{\text{Al}_2\text{O}_3}$

Electrolytic capacitors 电解电容器

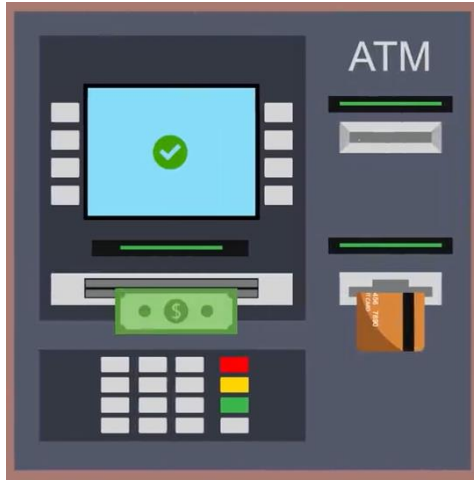


Solid electrolyte tantalum capacitor

6.5 Touchscreens

- ◆ **Resistive touchscreen**
- ◆ **Infrared touchscreen**
- ◆ **Surface acoustic wave touchscreen**
- ◆ **Capacitive touchscreen**

◆ Resistive touchscreen

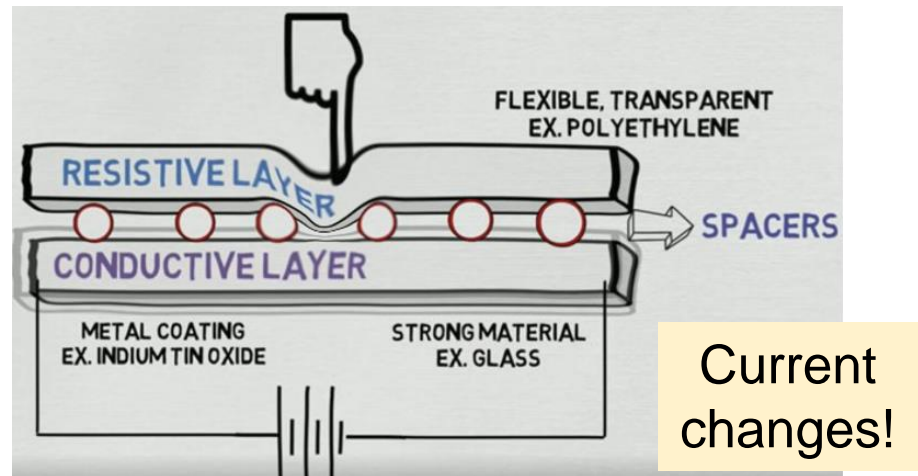
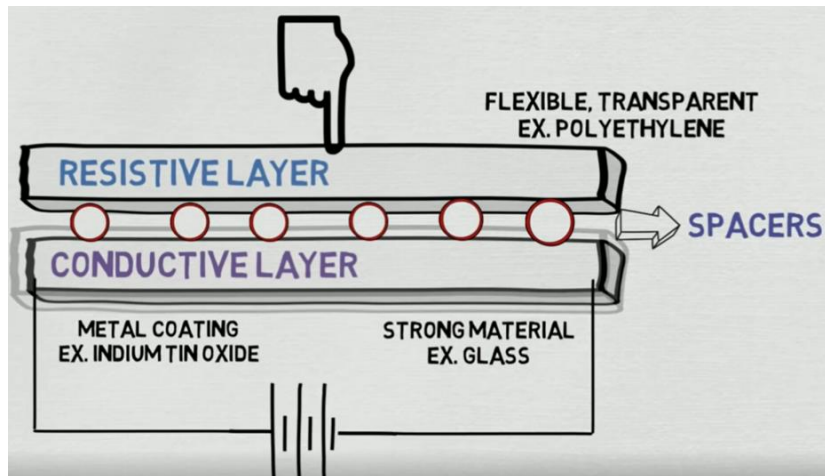


Advantages

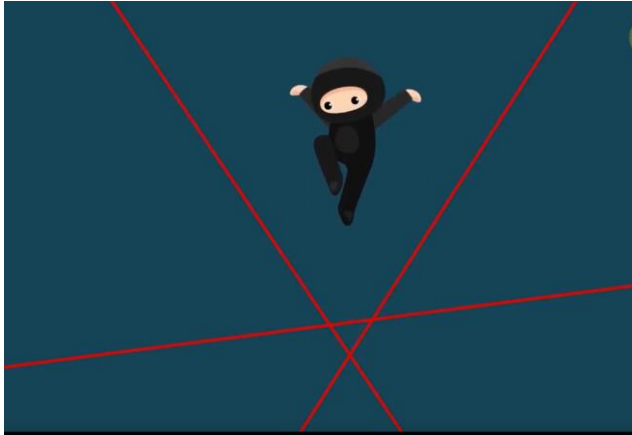
- Cheap
- Strong

Disadvantages

- Reflection
- No multitouch



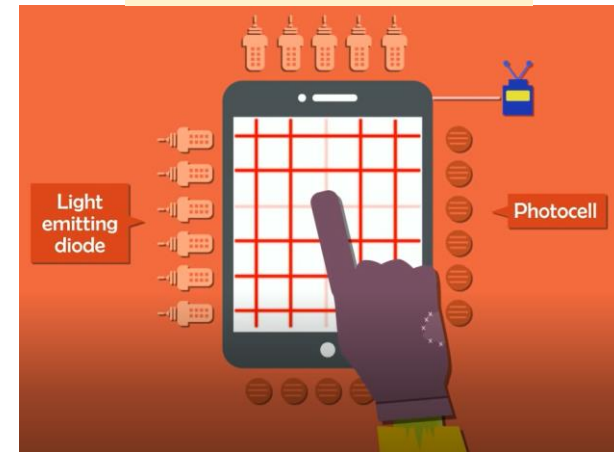
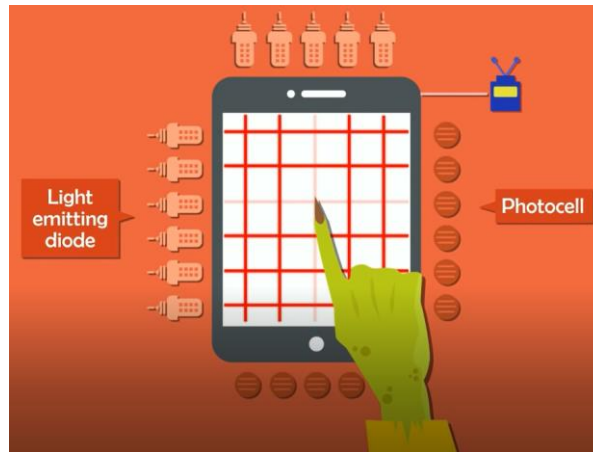
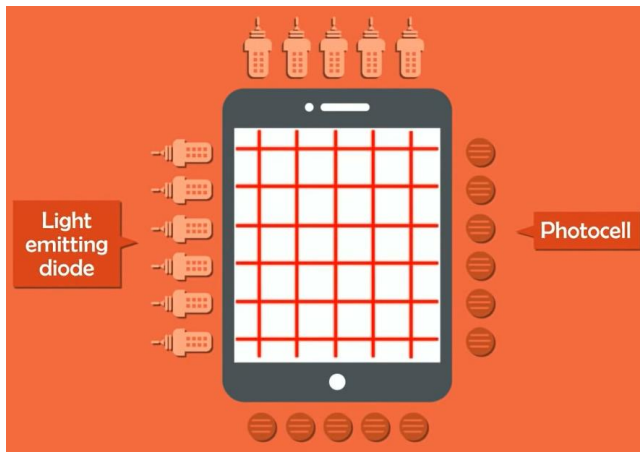
◆ Infrared touchscreen



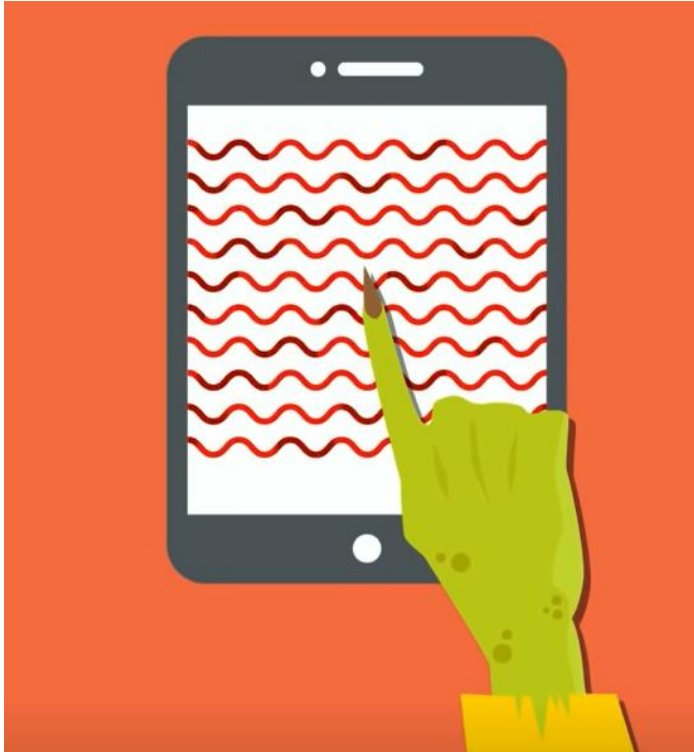
Some products:

- Amazon kindle touch
- Sony ebook readers

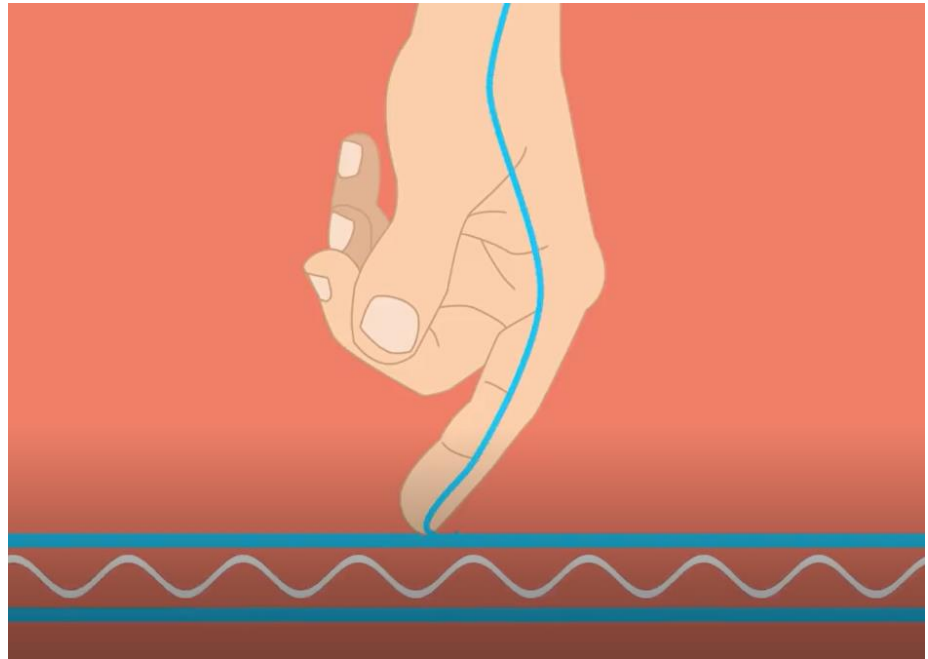
Ware gloves!



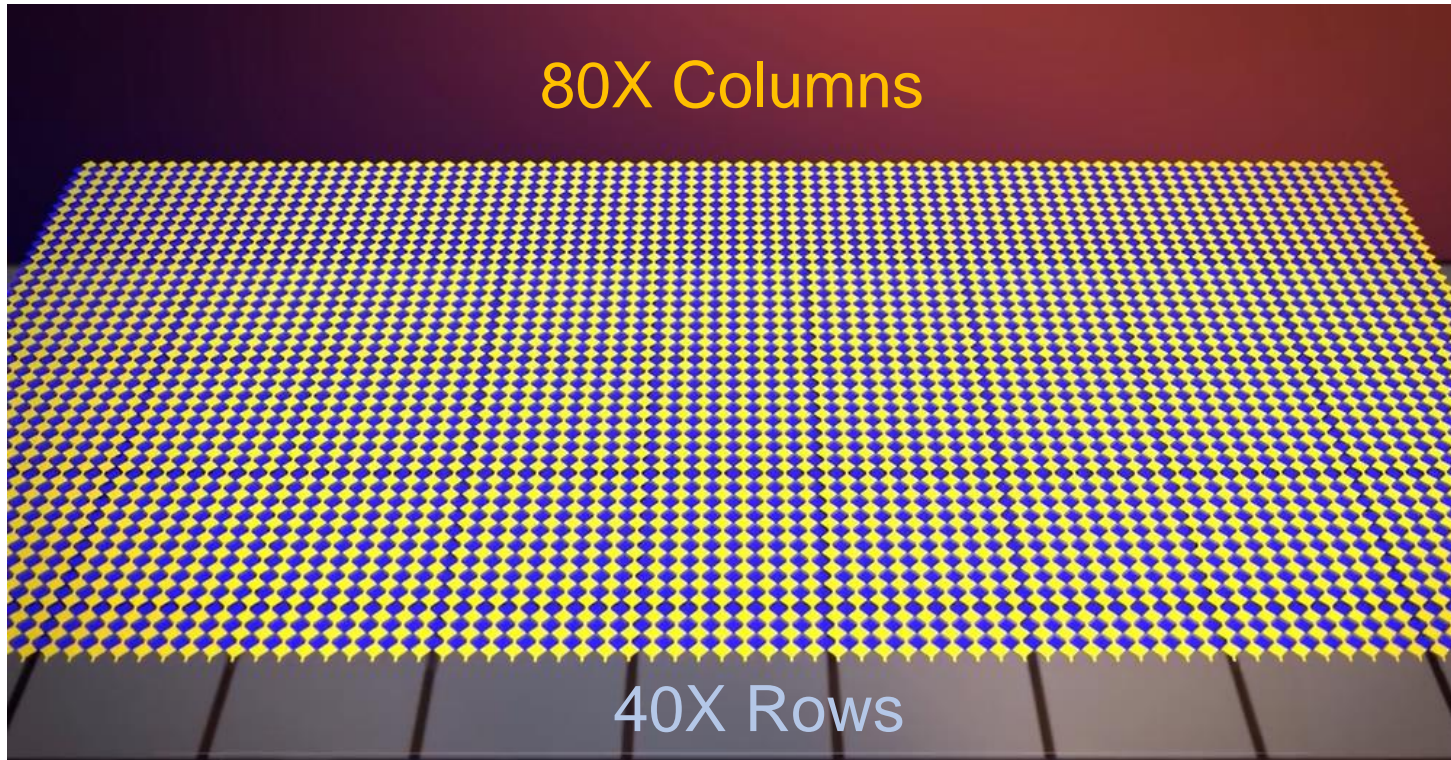
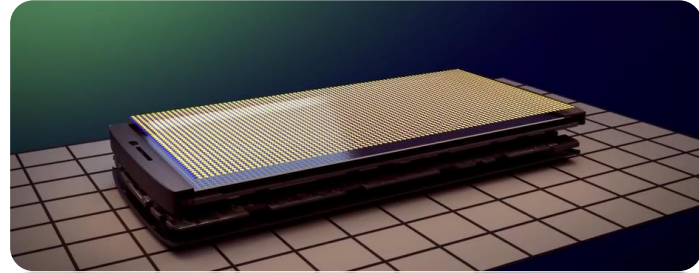
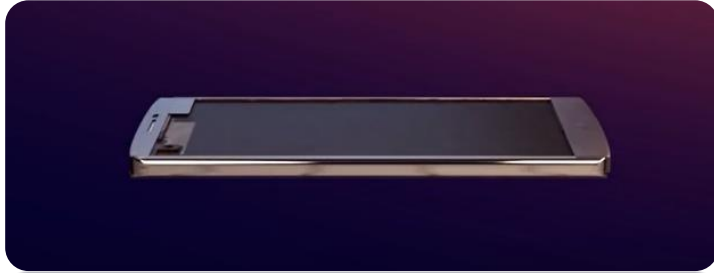
◆ Surface acoustic wave touchscreen



Use ultrasound wave to replace infrared light



◆ Capacitive touchscreen (Projective-type)



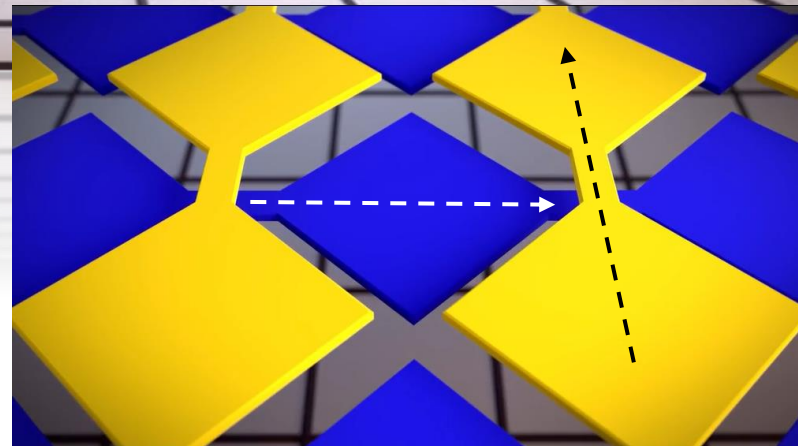
Top Grid

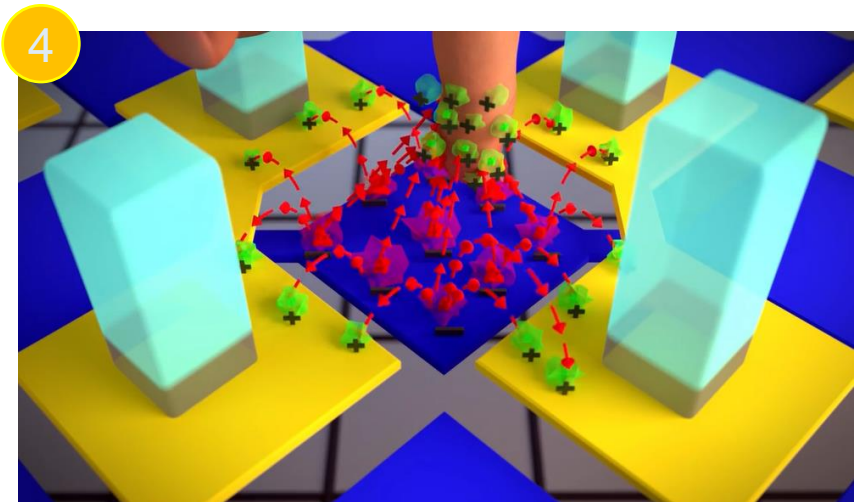
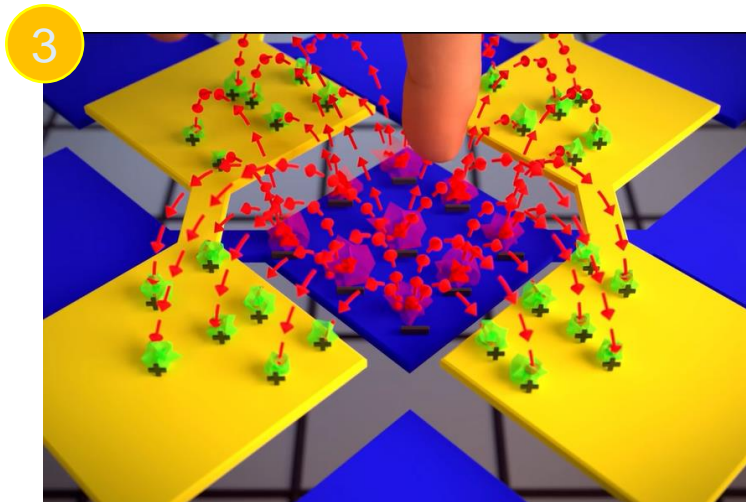
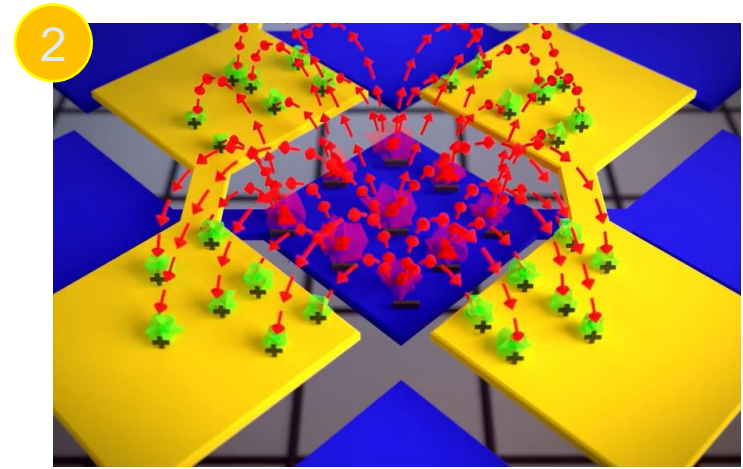
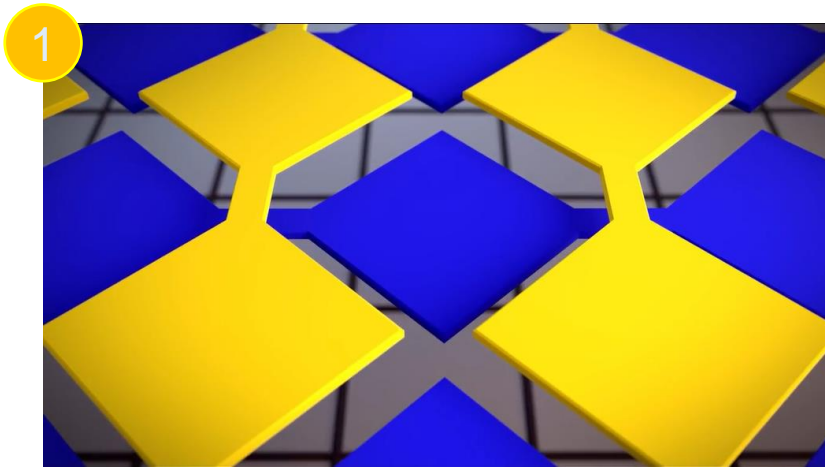


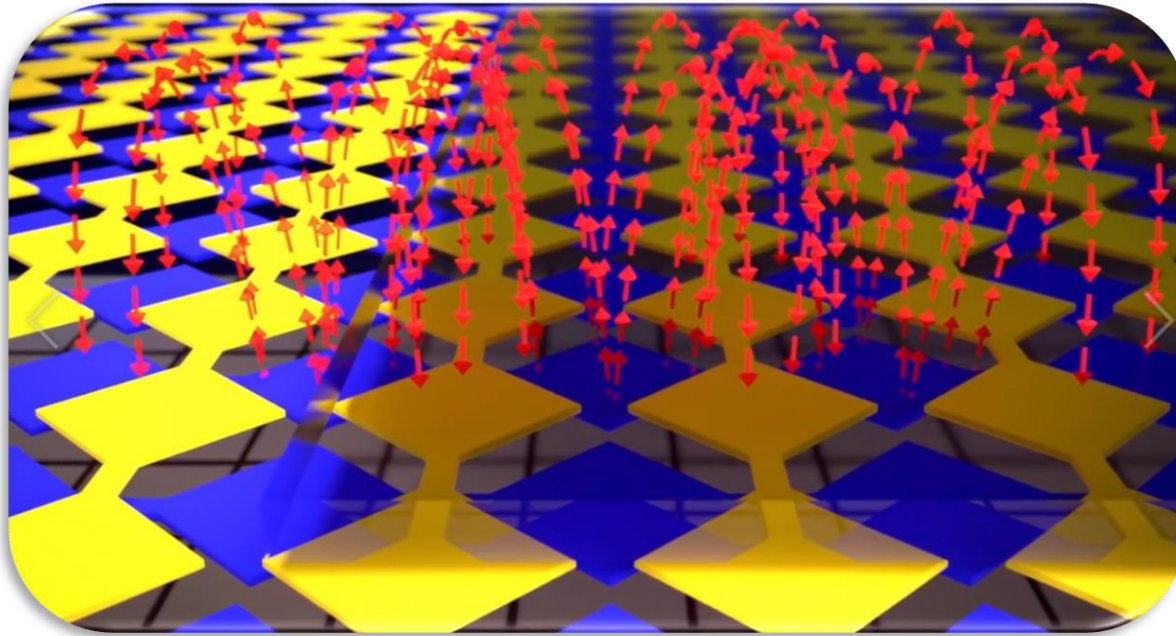
Clear Insulator



Bottom Grid

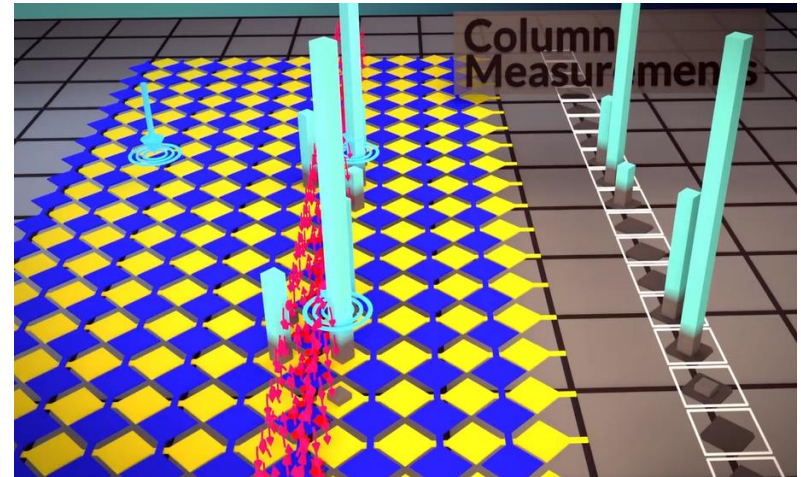
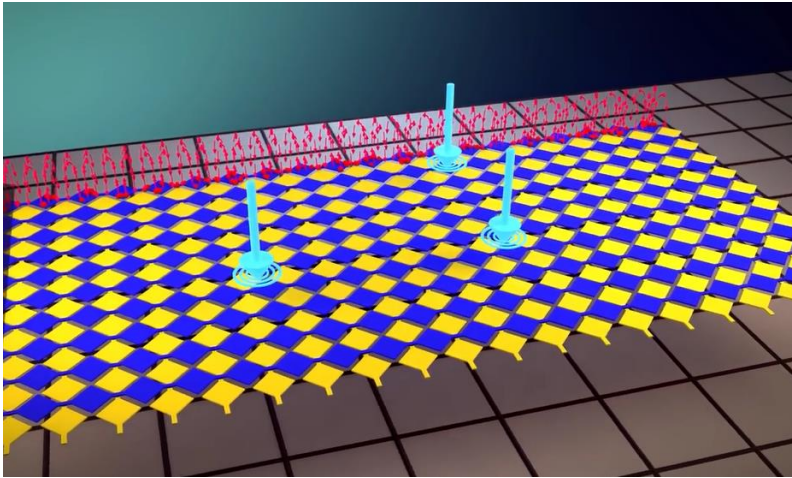




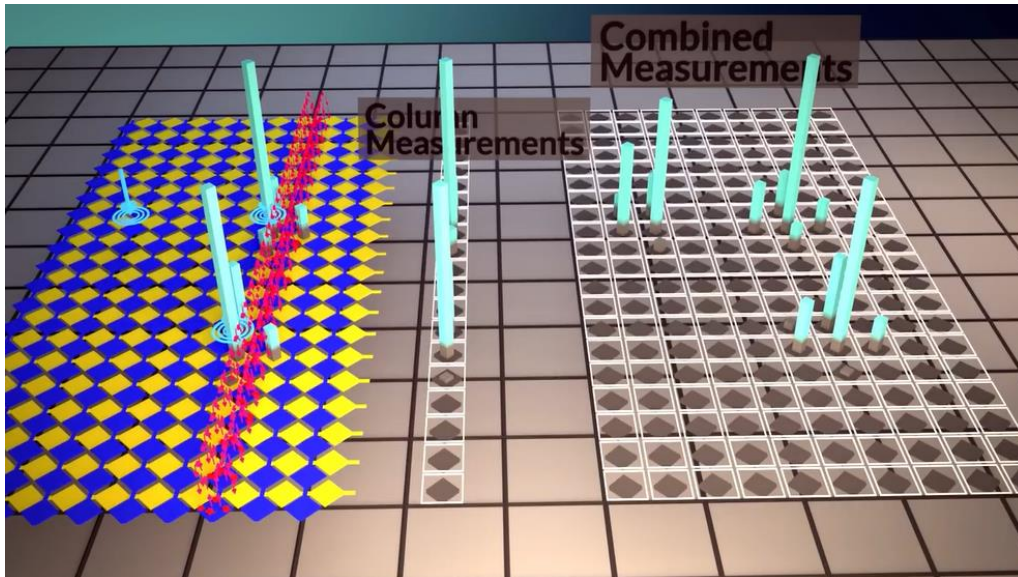


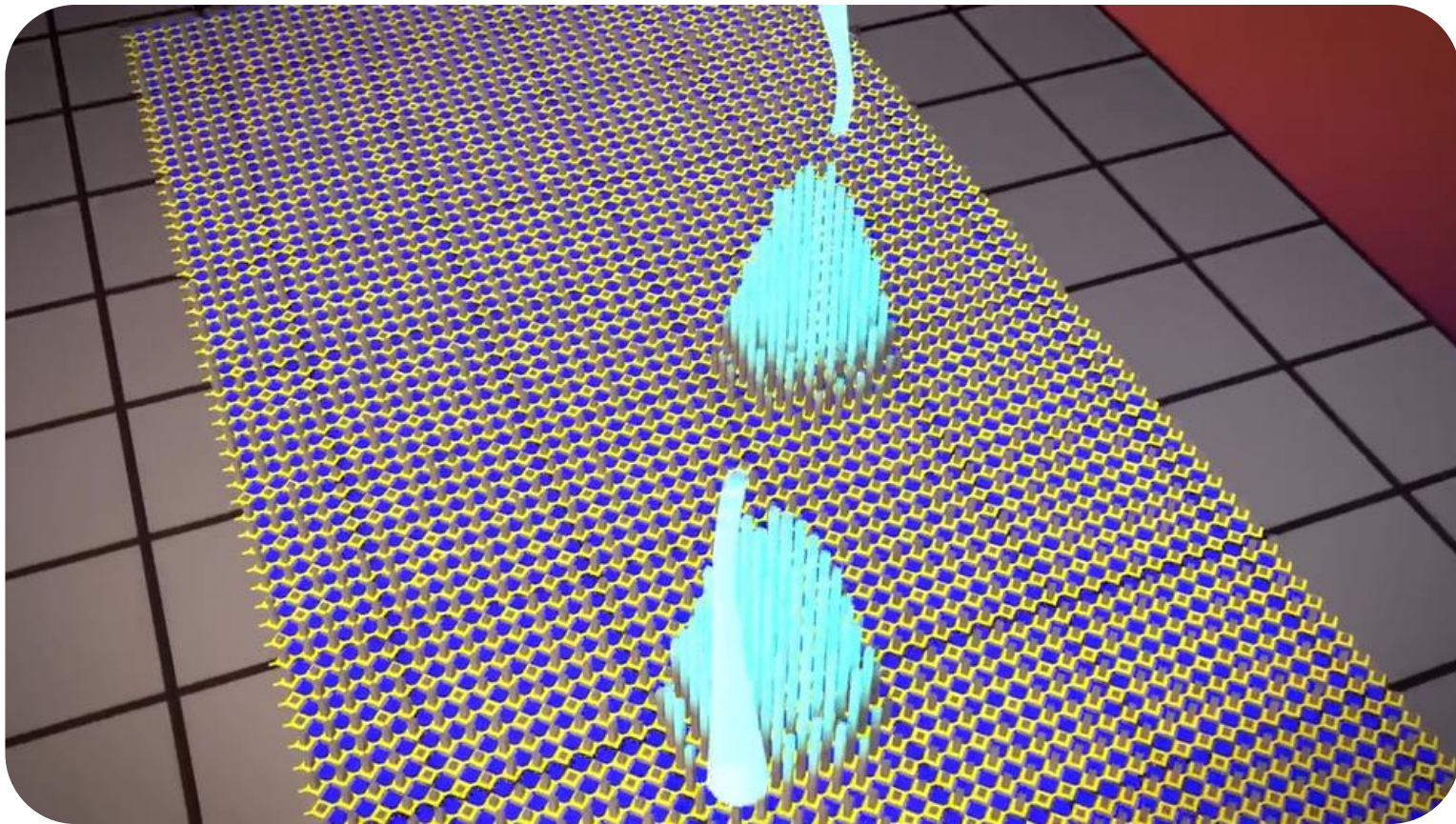
- Electric field can penetrate above the screen, so you even don't need to touch the screen.
- Can do multitouch.

◆ Multitouch capability



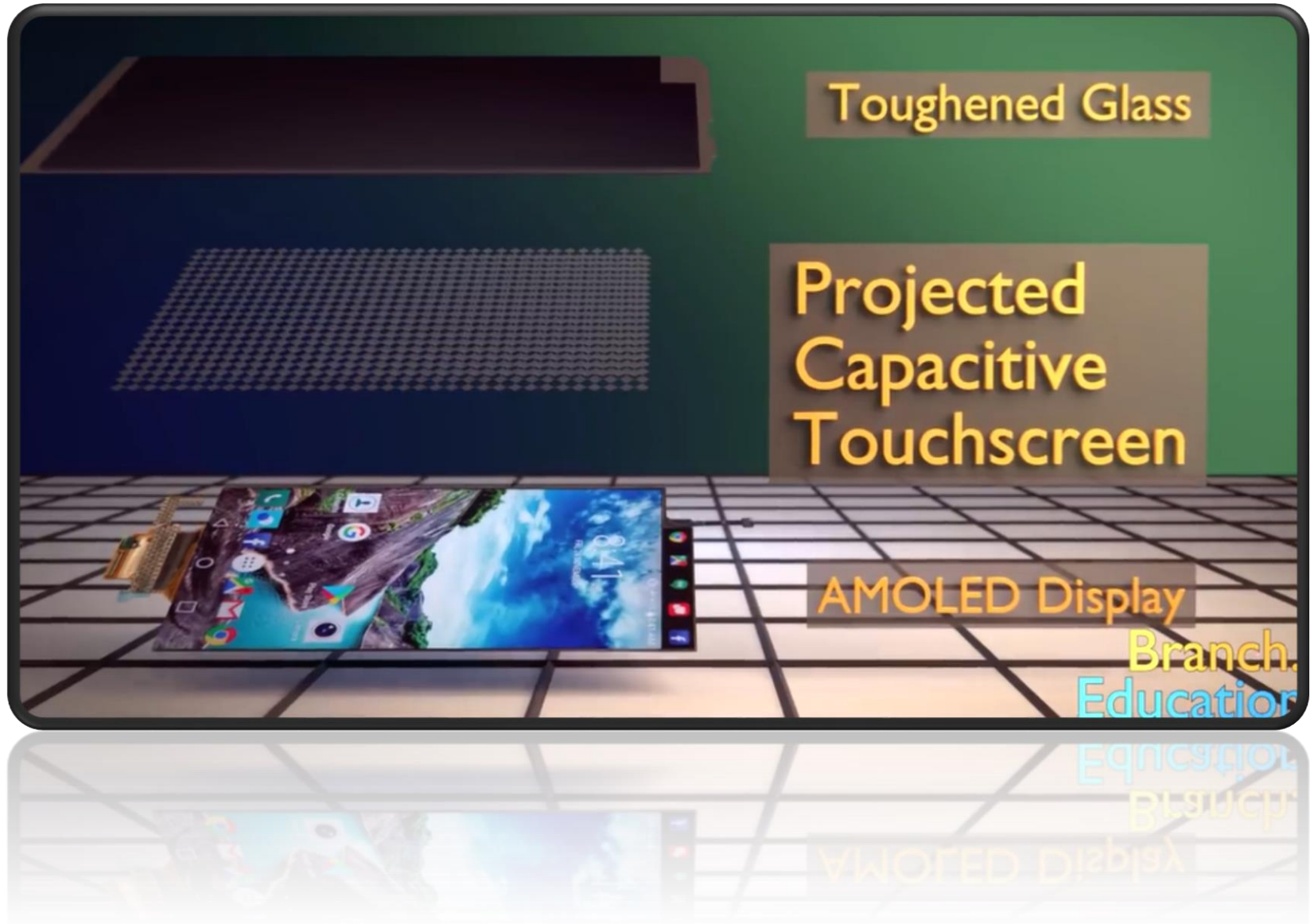
- 80 columns are electrically connected
- Scan each row within 10 μ s





Let's see a video

◆ Screen protector



Plastic Screen



Glass Screen



Shatter
Resistance



Scratch
Resistance



Cost



Aesthetic



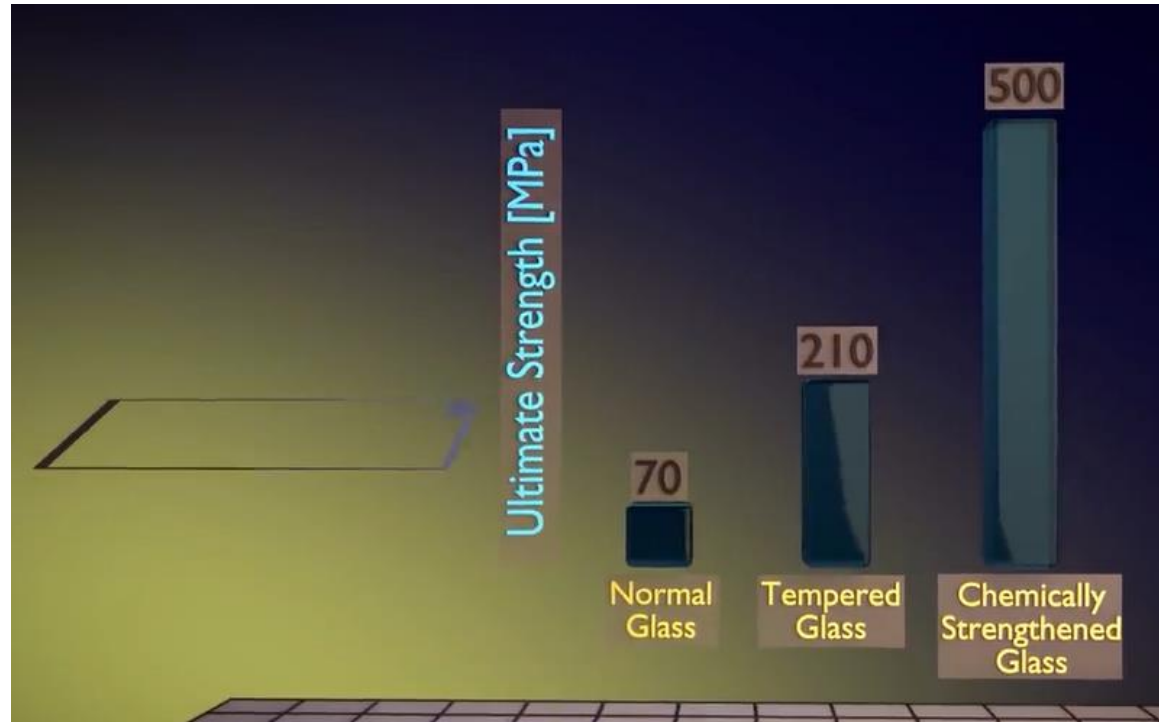
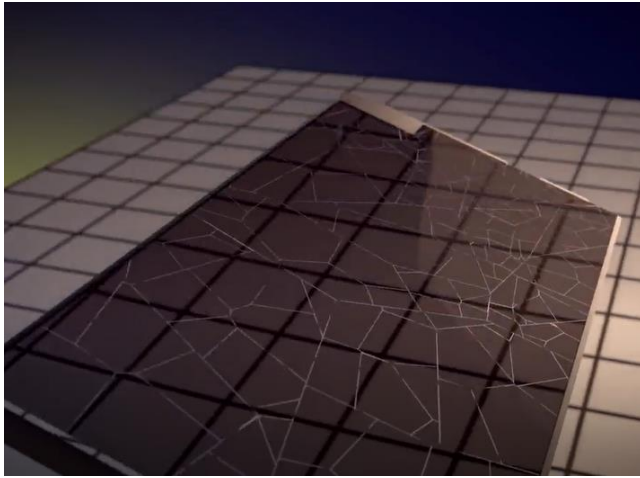
Branch.
Education

Aesthetic



Education
Branch

Glass screen



Chemically strengthened glass 化学钢化/强化玻璃

